256 MBit Synchronous DRAM

Preliminary Information

- High Performance:

	-8	-8A	-8B	Units
fCK	125	125	100	MHz
tCK3	8	8	10	ns
tAC3	6	6	6	ns
tCK2	10	12	15	ns
tAC2	6	6	7	ns

- Fully Synchronous to Positive Clock Edge
- 0 to 70 °C operating temperature
- Four Banks controlled by BA0 & BA1
- Programmable $\overline{\text{CAS}}$ Latency: 2, 3, 4
- Programmable Wrap Sequence: Sequential or Interleave
- Programmable Burst Length: 1, 2, 4, 8
- Multiple Burst Read with Single Write Operation
- Automatic and Controlled Precharge Command
- Data Mask for Read / Write control (x4, x8)
- Data Mask for byte control (x16)
- Auto Refresh (CBR) and Self Refresh
- Suspend Mode and Power Down Mode
- 8192 refresh cycles / 64 ms (7,8 µs)
- Random Column Address every CLK (1-N Rule)
- Single 3.3V +/- 0.3V Power Supply
- LVTTL Interface versions
- Plastic Packages: P-TSOPII-54 400mil width (x4, x8, x16)
- -8 parts for PC100 2-2-2 operation
  -8A parts for PC100 3-2-2 operation
  -8B parts for PC100 3-2-3 operation

The HYB39S256400/800/160T are four bank Synchronous DRAM's organized as 4 banks x 16MBit x4, 4 banks x 8MBit x8 and 4 banks x 4Mbit x16 respectively. These synchronous devices achieve high speed data transfer rates for CAS-latencies by employing a chip architecture that prefetches multiple bits and then synchronizes the output data to a system clock. The chip is fabricated with INFINEON's advanced 256MBit DRAM process technology.

The device is designed to comply with all industry standards set for synchronous DRAM products, both electrically and mechanically. All of the control, address, data input and output circuits are synchronized with the positive edge of an externally supplied clock.

Operating the four memory banks in an interleave fashion allows random access operation to occur at higher rate than is possible with standard DRAMs. A sequential and gapless data rate of is possible depending on burst length, $\overline{\text{CAS}}$ latency and speed grade of the device.

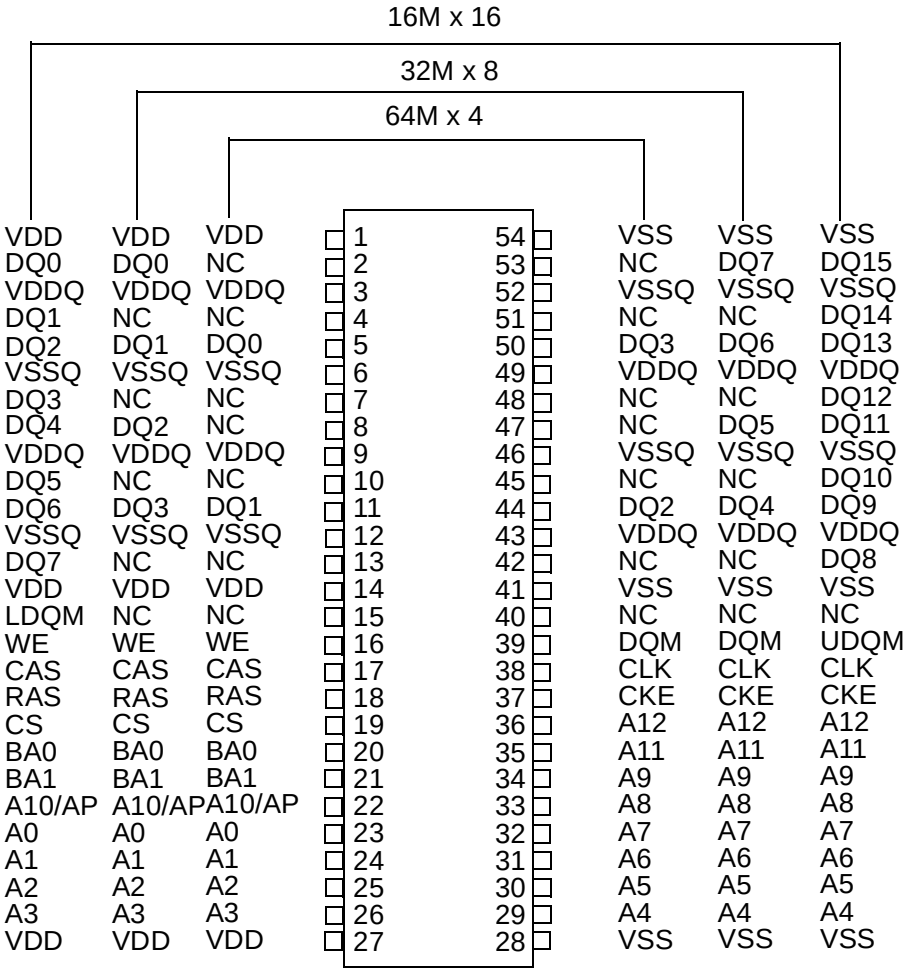
Auto Refresh (CBR) and Self Refresh operation are supported. These devices operates with a single 3.3V +/- 0.3V power supply and are available in TSOPII packages.

Ordering Information

Type	Speed Grade	Package	Description
LVTTL-version:			
HYB 39S256400T-8	PC100-222-620	P-TSOP-54-2 (400mil)	125MHz 4B x 16M x 4 SDRAM
HYB 39S256400T-8A	PC100-322-620	P-TSOP-54-2 (400mil)	125MHz 4B x 16M x 4 SDRAM
HYB 39S256400T-8B	PC100-323-620	P-TSOP-54-2 (400mil)	100MHz 4B x 16M x 4 SDRAM
HYB 39S256800T-8	PC100-222-620	P-TSOP-54-2 (400mil)	125MHz 4B x 8M x 8 SDRAM
HYB 39S256800T-8A	PC100-322-620	P-TSOP-54-2 (400mil)	125MHz 4B x 8M x 8 SDRAM
HYB 39S256800T-8B	PC100-323-620	P-TSOP-54-2 (400mil)	100MHz 4B x 8M x 8 SDRAM
HYB 39S256160T-8	PC100-222-620	P-TSOP-54-2 (400mil)	125MHz 4B x 4M x 16 SDRAM
HYB 39S256160T-8A	PC100-322-620	P-TSOP-54-2 (400mil)	125MHz 4B x 4M x 16 SDRAM
HYB 39S256160T-8B	PC100-323-620	P-TSOP-54-2 (400mil)	100MHz 4B x 4M x 16 SDRAM

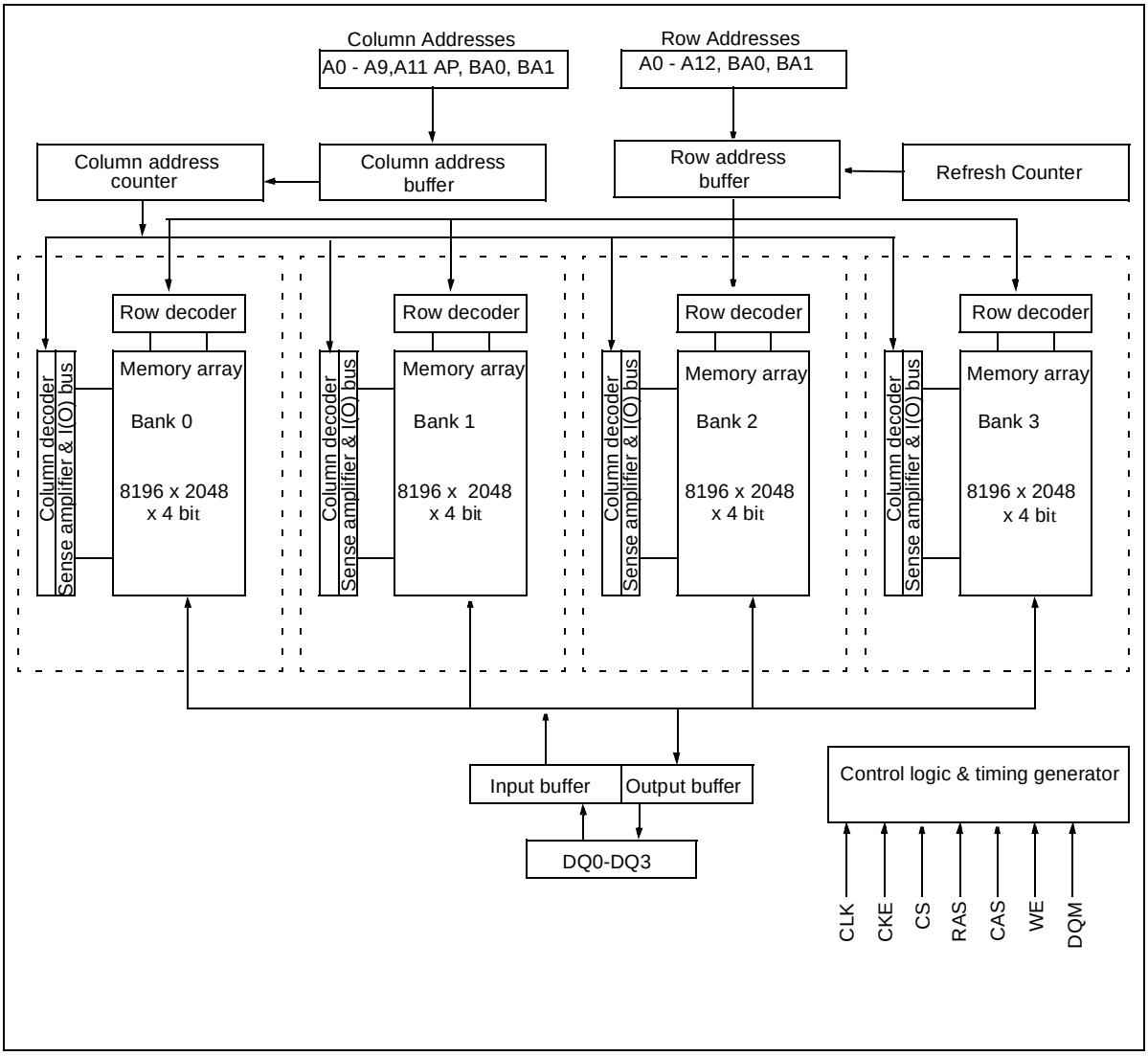
Pin Description and Pinouts:

CLK	Clock Input	**DQ**	Data Input /Output
CKE	Clock Enable	**DQM, LDQM, UDQM**	Data Mask
$\overline{CS}$	Chip Select	**Vdd**	Power (+3.3V)
$\overline{RAS}$	Row Address Strobe	**Vss**	Ground
$\overline{CAS}$	Column Address Strobe	**Vddq**	Power for DQ's (+ 3.3V)
$\overline{WE}$	Write Enable	**Vssq**	Ground for DQ's
A0-A12	Address Inputs	**NC**	not connected
BA0, BA1	Bank Select		

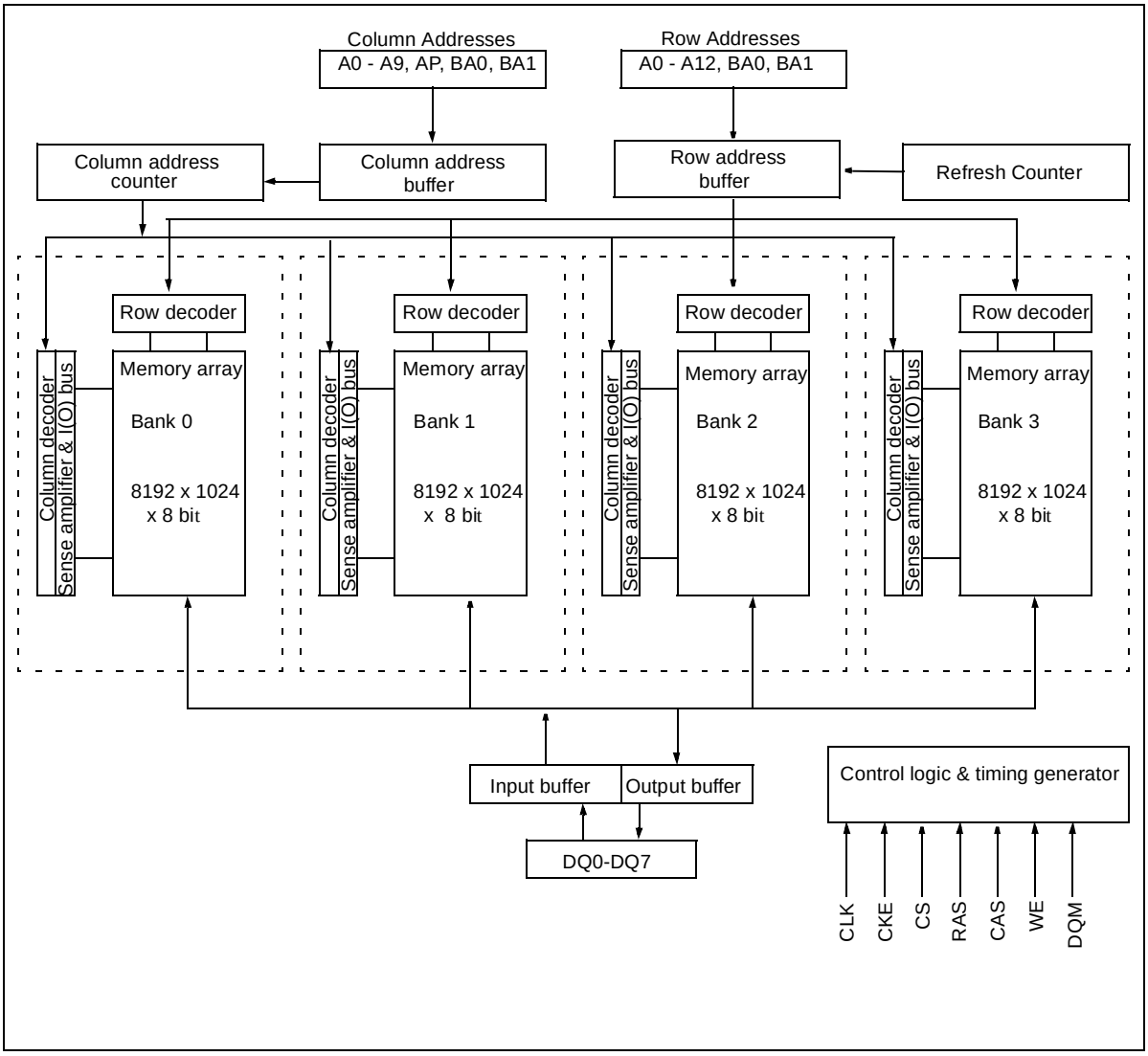


TSOPII-54 (400 mil x 875 mil, 0.8 mm pitch)

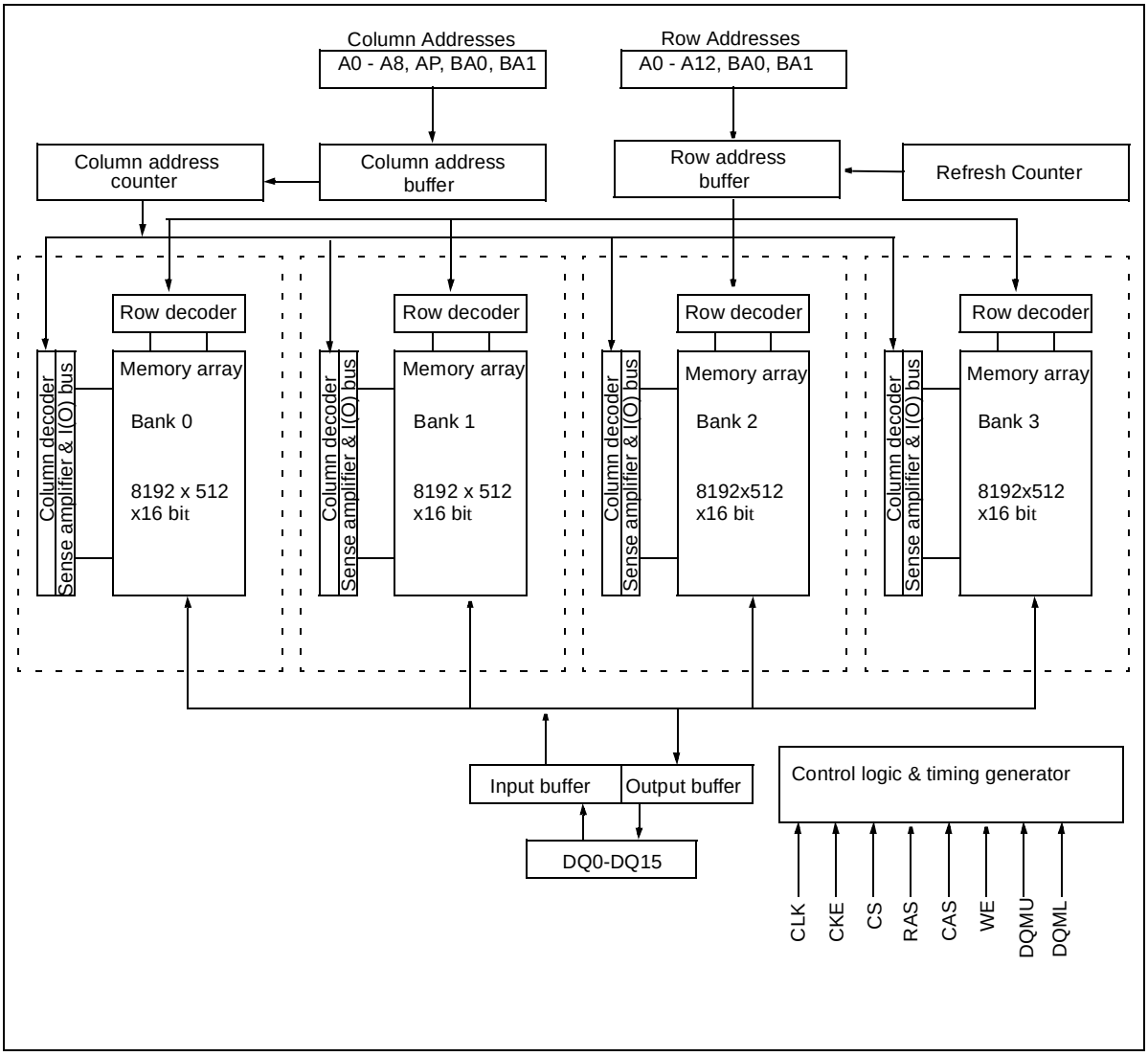
Pinout for x4, x8 & x16 organised 256M-DRAMs



Block Diagram for 64M x 4 SDRAM (13 / 11 / 2 addressing)



Block Diagram for 32M x 8 SDRAM (13 / 10 / 2 addressing)



Block Diagram for 16M x16 SDRAM (13 / 9 / 2 addressing)

Signal Pin Description

Pin	Type	Signal	Polarity	Function
CLK	Input	Pulse	Positive Edge	The system clock input. All of the SDRAM inputs are sampled on the rising edge of the clock.
CKE	Input	Level	Active High	Activates the CLK signal when high and deactivates the CLK signal when low, thereby initiates either the Power Down mode, Suspend mode, or the Self Refresh mode.
$\overline{CS}$	Input	Pulse	Active Low	$\overline{CS}$ enables the command decoder when low and disables the command decoder when high. When the command decoder is disabled, new commands are ignored but previous operations continue.
$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	Input	Pulse	Active Low	When sampled at the positive rising edge of the clock, $\overline{CAS}$, $\overline{RAS}$, and $\overline{WE}$ define the command to be executed by the SDRAM.
A0 - A12	Input	Level	—	During a Bank Activate command cycle, A0-A12 defines the row address (RA0-RA12) when sampled at the rising clock edge. During a Read or Write command cycle, A0-An defines the column address (CA0-CAn) when sampled at the rising clock edge.CAn depends from the SDRAM organisation: 64M x 4 SDRAM CAn = CA9,CA11 (Page Length = 2048 bits) 32M x 8 SDRAM CAn = CA9 (Page Length = 1024 bits) 16M x 16 SDRAM CAn = CA8 (Page Length = 512 bits) In addition to the column address, A10(=AP) is used to invoke autoprecharge operation at the end of the burst read or write cycle. If A10 is high, autoprecharge is selected and BA0, BA1 defines the bank to be precharged. If A10 is low, autoprecharge is disabled. During a Precharge command cycle, A10 (=AP) is used in conjunction with BA0 and BA1 to control which bank(s) to precharge. If A10 is high, all four banks will be precharged regardless of the state of BA0 and BA1. If A10 is low, then BA0 and BA1 are used to define which bank to precharge.
BA0,BA1	Input	Level	—	Bank Select Inputs. Bank address inputs selects which of the four banks a command applies to.
DQx	Input Output	Level	—	Data Input/Output pins operate in the same manner as on conventional DRAMs.
DQM LDQM UDQM	Input	Pulse	Active High	The Data Input/Output mask places the DQ buffers in a high impedance state when sampled high. In Read mode, DQM has a latency of two clock cycles and controls the output buffers like an output enable. In Write mode, DQM has a latency of zero and operates as a word mask by allowing input data to be written if it is low but blocks the write operation if DQM is high. One DQM input it present in x4 and x8 SDRAMs, LDQM and UDQM controls the lower and upper bytes in x16 SDRAMs.
VDD,VSS	Supply			Power and ground for the input buffers and the core logic.
VDDQ VSSQ	Supply	—	—	Isolated power supply and ground for the output buffers to provide improved noise immunity.

Operation Definition

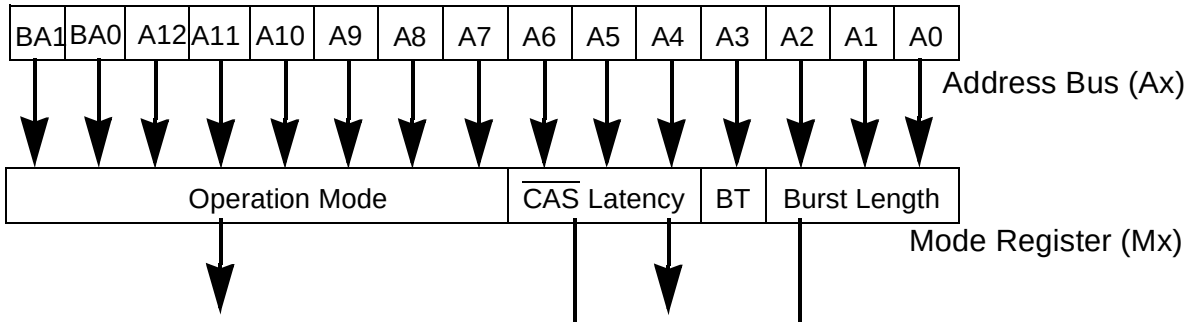
All of SDRAM operations are defined by states of control signals $\overline{CS}$, $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, and DQM at the positive edge of the clock. The following list shows the truth table for the operation commands.

Operation	Device State	CKE n-1	CKE n	DQM	BS0 BS1	AP= A10	Addr.	$\overline{CS}$	$\overline{RAS}$	$\overline{CAS}$	$\overline{WE}$
Bank Active	Idle[3]	H	X	X	V	V	V	L	L	H	H
Bank Precharge	Any	H	X	X	V	L	X	L	L	H	L
Precharge All	Any	H	X	X	X	H	X	L	L	H	L
Write	Active[3]	H	X	X	V	L	V	L	H	L	L
Write with Autoprecharge	Active[3]	H	X	X	V	H	V	L	H	L	L
Read	Active[3]	H	X	X	V	L	V	L	H	L	H
Read with Autoprecharge	Active[3]	H	X	X	V	H	V	L	H	L	H
Mode Register Set	Idle	H	X	X	V	V	V	L	L	L	L
No Operation	Any	H	X	X	X	X	X	L	H	H	H
Burst Stop	Active[4]	H	X	X	X	X	X	L	H	H	L
Device Deselect	Any	H	X	X	X	X	X	H	X	X	X
Auto Refresh	Idle	H	H	X	X	X	X	L	L	L	H
Self Refresh Entry	Idle	H	L	X	X	X	X	L	L	L	H
Self Refresh Exit	Idle (Self Refr.)	L	H	X	X	X	X	H	X	X	X
								L	H	H	X
Clock Suspend Entry	Active	H	L	X	X	X	X	X	X	X	X
Power Down Entry (Precharge or active standby)	Idle Active[5]	H	L	X	X	X	X	H	X	X	X
								L	H	H	X
Clock Suspend Exit	Active	L	H	X	X	X	X	X	X	X	X
Power Down Exit	Any (Power Down)	L	H	X	X	X	X	H	X	X	X
								L	H	H	L
Data Write/Output Enable	Active	H	X	L	X	X	X	X	X	X	X
Data Write/Output Disable	Active	H	X	H	X	X	X	X	X	X	X

Note:

1. V = Valid, x = Don't Care, L = Low Level, H = High Level
2. CKEn signal is input level when commands are provided, CKEn-1 signal is input level one clock before the commands are provided.
3. This is the state of the banks designated by BA0, BA1 signals.
4. Device state is Full Page Burst operation, which is not supported on this device.
5. Power Down Mode can not entry in the burst cycle. When this command assert in the burst mode cycle device is clock suspend mode.

Address Input for Mode Set (Mode Register Operation)



Operation Mode

M9	Mode
0	burst read / burst write
1	burst read / single write

Burst Type

M3	Type
0	Sequential
1	Interleave

$\overline{\text{CAS}}$ Latency

M6	M5	M4	Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	2
0	1	1	3
1	0	0	4
1	0	1	Reserved
1	1	0	
1	1	1	

Burst Length

M2	M1	M0	Length	
			Sequential	Interleave
0	0	0	1	1
0	0	1	2	2
0	1	0	4	4
0	1	1	8	8
1	0	0	Reserved	Reserved
1	0	1		
1	1	0		
1	1	1		

Power On and Initialization

The default power on state of the mode register is supplier specific and may be undefined. The following power on and initialization sequence guarantees the device is preconditioned to each users specific needs. Like a conventional DRAM, the Synchronous DRAM must be powered up and initialized in a predefined manner.During power on, all VDD and VDDQ pins must be built up simultaneously to the specified voltage when the input signals are held in the “NOP” state. The power on voltage must not exceed VDD+0.3V on any of the input pins or VDD supplies. The CLK signal must be started at the same time. After power on, an initial pause of 200 µs is required followed by a precharge of all banks using the precharge command. To prevent data contention on the DQ bus during power on, it is required that the DQM and CKE pins be held high during the initial pause period. Once all banks have been precharged, the Mode Register Set Command must be issued to initialize the Mode Register. A minimum of eight Auto Refresh cycles (CBR) are also required.These may be done before or after programming the Mode Register. Failure to follow these steps may lead to unpredictable start-up modes.

Programming the Mode Register

The Mode register designates the operation mode at the read or write cycle. This register is divided into 4 fields. A Burst Length Field to set the length of the burst, an Addressing Selection bit to program the column access sequence in a burst cycle (interleaved or sequential), a CAS **Latency** Field to set the access time at clock cycle and a Operation mode field to differentiate between normal operation (Burst read and burst Write) and a special Burst Read and Single Write mode. The mode set operation must be done before any activate command after the initial power up. Any content of the mode register can be altered by re-executing the mode set command. All banks must be in precharged state and CKE must be high at least one clock before the mode set operation. After the mode register is set, a Standby or NOP command is required. Low signals of $\overline{RAS}$, $\overline{CAS}$, and $\overline{WE}$ at the positive edge of the clock activate the mode set operation. Address input data at this timing defines parameters to be set as shown in the previous table.

Read and Write Operation

When $\overline{RAS}$ is low and both $\overline{CAS}$ and $\overline{WE}$ are high at the positive edge of the clock, a RAS cycle starts. According to address data, a word line of the selected bank is activated and all of sense amplifiers associated to the wordline are set. A CAS cycle is triggered by setting $\overline{RAS}$ high and $\overline{CAS}$ low at a clock timing after a necessary delay, t_{RCD}, from the RAS timing. $\overline{WE}$ is used to define either a read ($\overline{WE}$ = H) or a write ($\overline{WE}$ = L) at this stage.

SDRAM provides a wide variety of fast access modes. In a single CAS cycle, serial data read or write operations are allowed at up to a 143 MHz data rate. The numbers of serial data bits are the burst length programmed at the mode set operation, i.e., one of 1, 2, 4 and 8. Column addresses are segmented by the burst length and serial data accesses are done within this boundary. The first column address to be accessed is supplied at the CAS timing and the subsequent addresses are generated automatically by the programmed burst length and its sequence. For example, in a burst length of 8 with interleave sequence, if the first address is ‘2’, then the rest of the burst sequence is 3, 0, 1, 6, 7, 4, and 5.

Similar to the page mode of conventional DRAM’s, burst read or write accesses on any column address are possible once the RAS cycle latches the sense amplifiers. The maximum tRAS or the refresh interval time limits the number of random column accesses. A new burst access can be done even before the previous burst ends. The interrupt operation at every clock cycle is supported.

When the previous burst is interrupted, the remaining addresses are overridden by the new address with the full burst length. An interrupt which accompanies an operation change from a read to a write is possible by exploiting DQM to avoid bus contention.

When two or more banks are activated sequentially, interleaved bank read or write operations are possible. With the programmed burst length, alternate access and precharge operations on two or more banks can realize fast serial data access modes among many different pages. Once two or more banks are activated, column to column interleave operation can be performed between different pages.

Burst Length and Sequence:

Burst Length	Starting Address (A2 A1 A0)	Sequential Burst Addressing (decimal)	Interleave Burst Addressing (decimal)
2	xx0 xx1	0, 1 1, 0	0, 1 1, 0
4	x00 x01 x10 x11	0, 1, 2, 3 1, 2, 3, 0 2, 3, 0, 1 3, 0, 1, 2	0, 1, 2, 3 1, 0, 3, 2 2, 3, 0, 1 3, 2, 1, 0
8	000 001 010 011 100 101 110 111	0 1 2 3 4 5 6 7 1 2 3 4 5 6 7 0 2 3 4 5 6 7 0 1 3 4 5 6 7 0 1 2 4 5 6 7 0 1 2 3 5 6 7 0 1 2 3 4 6 7 0 1 2 3 4 5 7 0 1 2 3 4 5 6	0 1 2 3 4 5 6 7 1 0 3 2 5 4 7 6 2 3 0 1 6 7 4 5 3 2 1 0 7 6 5 4 4 5 6 7 0 1 2 3 5 4 7 6 1 0 3 2 6 7 4 5 2 3 0 1 7 6 5 4 3 2 1 0

Refresh Mode

SDRAM has two refresh modes, Auto Refresh and Self Refresh. Auto Refresh is similar to the $\overline{CAS}$ -before-$\overline{RAS}$ refresh of conventional DRAMs. All of banks must be precharged before applying any refresh mode. An on-chip address counter increments the word and the bank addresses and no bank information is required for both refresh modes.

The chip enters the Auto Refresh mode, when $\overline{RAS}$ and $\overline{CAS}$ are held low and CKE and $\overline{WE}$ are held high at a clock timing. The mode restores word line after the refresh and no external precharge command is necessary. A minimum tRC time is required between two automatic refreshes in a burst refresh mode. The same rule applies to any access command after the automatic refresh operation.

The chip has an on-chip timer and the Self Refresh mode is available. The mode restores the word lines after $\overline{RAS}$, $\overline{CAS}$, and CKE are low and $\overline{WE}$ is high at a clock timing. All of external control signals including the clock are disabled. Returning CKE to high enables the clock and initiates the refresh exit operation. After the exit command, at least one tRC delay is required prior to any access command.

DQM Function

DQM has two functions for data I/O read and write operations. During reads, when it turns to „high“ at a clock timing, data outputs are disabled and become high impedance after two clock delay (DQM Data Disable Latency t_{DQZ}). It also provides a data mask function for writes. When DQM is activated, the write operation at the next clock is prohibited (DQM Write Mask Latency t_{DQW} = zero clocks).

Suspend Mode

During normal access mode, CKE is held high enabling the clock. When CKE is low, it freezes the internal clock and extends data read and write operations. One clock delay is required for mode entry and exit (Clock Suspend Latency t_{CSL}).

Power Down

In order to reduce standby power consumption, a power down mode is available. All banks must be precharged and the necessary Precharge delay (trp) must occur before the SDRAM can enter the Power Down mode. Once the Power Down mode is initiated by holding CKE low, all of the receiver circuits except CLK and CKE are gated off. The Power Down mode does not perform any refresh operations, therefore the device can’t remain in Power Down mode longer than the Refresh period (tref) of the device. Exit from this mode is performed by taking CKE „high“. One clock delay is required for mode entry and exit.

Auto Precharge

Two methods are available to precharge SDRAMs. In an automatic precharge mode, the CAS timing accepts one extra address, CA10, to determine whether the chip restores or not after the operation. If CA10 is high when a Read Command is issued, the **Read with Auto-Precharge** function is initiated. The SDRAM automatically enters the precharge operation one clock before the last data out for $\overline{CAS}$ latencies 2, two clocks for $\overline{CAS}$ latencies 3 and three clocks for CAS latencies 4. If CAS10 is high when a Write Command is issued, the **Write with Auto-Precharge** function is initiated. The SDRAM automatically enters the precharge operation a time delay equal to t_{WR} (Write recovery time) after the last data in.

Precharge Command

There is also a separate precharge command available. When $\overline{RAS}$ and $\overline{WE}$ are low and $\overline{CAS}$ is high at a clock timing, it triggers the precharge operation. Three address bits, BA0, BA1 and A10 are used to define banks as shown in the following list. The precharge command can be imposed one clock before the last data out for CAS latency = 2, two clocks before the last data out for CAS latency = 3 and three clocks before the last data out for CAS latency= 4. Writes require a time delay twr from the last data out to apply the precharge command.

Bank Selection by Address Bits

A10	BA0	BA1	
0	0	0	Bank 0
0	0	1	Bank 1
0	1	0	Bank 2
0	1	1	Bank 3
1	x	x	all Banks

Burst Termination

Once a burst read or write operation has been initiated, there are several methods in which to terminate the burst operation prematurely. These methods include using another Read or Write Command to interrupt an existing burst operation, use a Precharge Command to interrupt a burst cycle and close the active bank, or using the Burst Stop Command to terminate the existing burst operation but leave the bank open for future Read or Write Commands to the same page of the active bank. When interrupting a burst with another Read or Write Command care must be taken to avoid DQ contention. The Burst Stop Command, however, has the fewest restrictions making it the easiest method to use when terminating a burst operation before it has been completed. If a Burst Stop command is issued during a burst write operation, then any residual data from the burst write cycle will be ignored. Data that is presented on the DQ pins before the Burst Stop Command is registered will be written to the memory.

Absolute Maximum Ratings

Operating temperature range .....0 to + 70 °C
Storage temperature range.....– 55 to + 150 °C
Input/output voltage ..... – 0.3 to Vcc+0.3 V
Power supply voltage VDD / VDDQ..... – 0.3 to + 4.6 V
Power Dissipation..... .....1 W
Data out current (short circuit) ..... 50 mA

Note: *Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage of the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

Recommended Operation and Characteristics:

T_A = 0 to 70 °C; V_{SS} = 0 V; V_{DD}, V_{DDQ} = 3.3 V ± 0.3 V

Parameter	Symbol	Limit Values		Unit	Notes
		min.	max.		
Input high voltage	V_{IH}	2.0	Vcc+0.3	V	1, 2
Input low voltage	V_{IL}	– 0.3	0.8	V	1, 2
Output high voltage (I_{OUT} = – 4.0 mA)	V_{OH}	2.4	–	V	3
Output low voltage (I_{OUT} = 4.0 mA)	V_{OL}	–	0.4	V	3
Input leakage current, any input (0 V < V_{IN} < Vddq, all other inputs = 0 V)	$I_{I(L)}$	– 5	5	µA	
Output leakage current (DQ is disabled, 0 V < V_{OUT} < V_{CC})	$I_{O(L)}$	– 5	5	µA	

Notes:

1. All voltages are referenced to VSS.
2. Vih may overshoot to Vcc + 2.0 V for pulse width of < 4ns with 3.3V. Vil may undershoot to -2.0 V for pulse width < 4.0 ns with 3.3V. Pulse width measured at 50% points with amplitude measured peak to DC reference.

Capacitance

T_A = 0 to 70 °C; V_{DD} = 3.3 V ± 0.3 V, f = 1 MHz

Parameter	Symbol	Values		Unit
		min.	max.	
Input capacitance (CLK)	C_{I1}	2.5	4.0	pF
Input capacitance (A0-A12, BA0,BA1,$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{CS}$, CKE, DQM)	C_{I2}	2.5	5.0	pF
Input / Output capacitance (DQ)	C_{IO}	4.0	6.5	pF

Operating Currents (T_A = 0 to 70°C, Vdd = 3.3V ± 0.3V

(Recommended Operating Conditions unless otherwise noted)

Parameter & Test Condition		Symb.	-8/-8A	-8B		Note
			max.			
OPERATING CURRENT trc=trcmin., tck=tckmin. Ouputs open, Burst Length = 4, CL=3 All banks operated in random access, all banks operated in ping-pong manner to maximize gapless data access		ICC1 x4 x8 x16	 210 210 210	 165 165 165	 mA mA mA	 3
PRECHARGE STANDBY CURRENT in Power Down Mode $\overline{CS}$ =VIH (min.), CKE<=Vil(max)	tck = min.	ICC2P	2	2	mA	3
PRECHARGE STANDBY CURRENT in Non-Power Down Mode $\overline{CS}$ = VIH (min.), CKE>=Vih(min)	tck = min.	ICC2N	19	16	mA	3
NO OPERATING CURRENT tck = min., $\overline{CS}$ = VIH(min), active state (max. 4 banks)	CKE>=VIH(min.)	ICC3N	45	40	mA	3
	CKE<=VIL(max.)	ICC3P	10	10	mA	3
BURST OPERATING CURRENT tck = min., Read command cycling		ICC4 x4 x8 x16	 210 210 210	 165 165 165	 mA mA mA	 3,4
AUTO REFRESH CURRENT tck = min., Auto Refresh command cycling		ICC5	240	195	mA	3
SELF REFRESH CURRENT Self Refresh Mode, CKE=0.2V	standard version	ICC6	2.5	2.5	mA	3

Notes:

3. These parameters depend on the cycle rate. These values are measured at 125 MHz for -8 & -8A and at 100 MHz for -10 parts. Input signals are changed once during tck, excepts for ICC6 and for standby currents when tck=infinity.
4. These parameters are measured with continuous data stream during read access and all DQ toggling. CL=3 and BL=4 is assumed and the VDDQ current is excluded.

AC Characteristics 1)2)
T_A = 0 to 70 °C; V_{SS} = 0 V; Vdd = 3.3 V ± 0.3 V, t_T = 1 ns

Parameter	Symbol	Limit Values						Unit	
		-8 PC100-222		-8A PC100-322		-8B PC100-323			
		min.	max.	min.	max.	min.	max.		
Clock and Clock Enable									
Clock Cycle Time									
$\overline{\text{CAS}}$ Latency = 3	t_{CK}	8	–	8	–	10	–	ns	
$\overline{\text{CAS}}$ Latency = 2		10	–	12	–	15	–	ns	
Clock Frequency									
$\overline{\text{CAS}}$ Latency = 3	t_{CK}	–	125	–	125	–	100	MHz	
$\overline{\text{CAS}}$ Latency = 2		–	100	–	83	–	66	MHz	
Access Time from Clock									
$\overline{\text{CAS}}$ Latency = 3	t_{AC}	–	6	–	6	–	6	ns	2, 3
$\overline{\text{CAS}}$ Latency = 2		–	6	–	6	–	7	ns	
Clock High Pulse Width	t_{CH}	3	–	3	–	3	–	ns	
Clock Low Pulse Width	t_{CL}	3	–	3	–	3	–	ns	
Transition time	t_T	0.5	10	0.5	10	0.5	10	ns	
Setup and Hold Times									
Input Setup Time	t_{IS}	2	–	2	–	2	–	ns	4
Input Hold Time	t_{IH}	1	–	1	–	1	–	ns	4
CKE Setup Time	t_{CKS}	2	–	2	–	2	–	ns	4
CKE Hold Time	t_{CKH}	1	–	1	–	1	–	ns	4
Mode Register Set-up time	t_{RSC}	16	–	16	–	20	–	ns	
Power Down Mode Entry Time	t_{SB}	0	8	0	10	0	10	ns	
Common Parameters									
Row to Column Delay Time	t_{RCD}	20	–	20		20	–	ns	5
Row Precharge Time	t_{RP}	20	–	20		30	–	ns	5
Row Active Time	t_{RAS}	48	100k	48	100k	60	100k	ns	5
Row Cycle Time	t_{RC}	70	–	70	–	80	–	ns	5

Parameter	Symbol	Limit Values						Unit	
		-8 PC100-222		-8A PC100-322		-8B PC100-323			
		min.	max.	min.	max.	min.	max.		
Activate(a) to Activate(b) Command period	t_{RRD}	16	–	16		20	–	ns	5
$\overline{CAS}$(a) to $\overline{CAS}$(b) Command period	t_{CCD}	1	–	1	–	1	–	CLK	
Refresh Cycle									
Refresh Period (8192 cycles)	t_{REF}	–	64	–	64	–	64	ms	
Self Refresh Exit Time	t_{SREX}	10		10		10		ns	
Read Cycle									
Data Out Hold Time	t_{OH}	3	–	3	–	3	–	ns	2
Data Out to Low Impedance Time	t_{LZ}	0	–	0	–	0	–	ns	
Data Out to High Impedance Time	t_{HZ}	3	8	3	8	3	10	ns	
DQM Data Out Disable Latency	t_{DQZ}	–	2	–	2	–	2	CLK	
Write Cycle									
Data Input to Precharge (write recovery)	t_{WR}	2	–	2	–	2	–	CLK	
DQM Write Mask Latency	t_{DQW}	0	–	0	–	0	–	CLK	

Notes for AC Parameters:

1. For proper power-up see the operation section of this data sheet.
2. AC timing tests for LV-TTL versions have V_{il} = 0.4 V and V_{ih} = 2.4 V with the timing referenced to the 1.4 V crossover point. The transition time is meas ured between V_{ih} and V_{il}. All AC measurements assume t_T=1ns with the AC output load circuit shown in fig.1.Specified tac and toh parameters are measured with a 50 pF only, without any resistive termination and with a input signal of 1V / ns edge rate between 0.8V and 2.0 V.

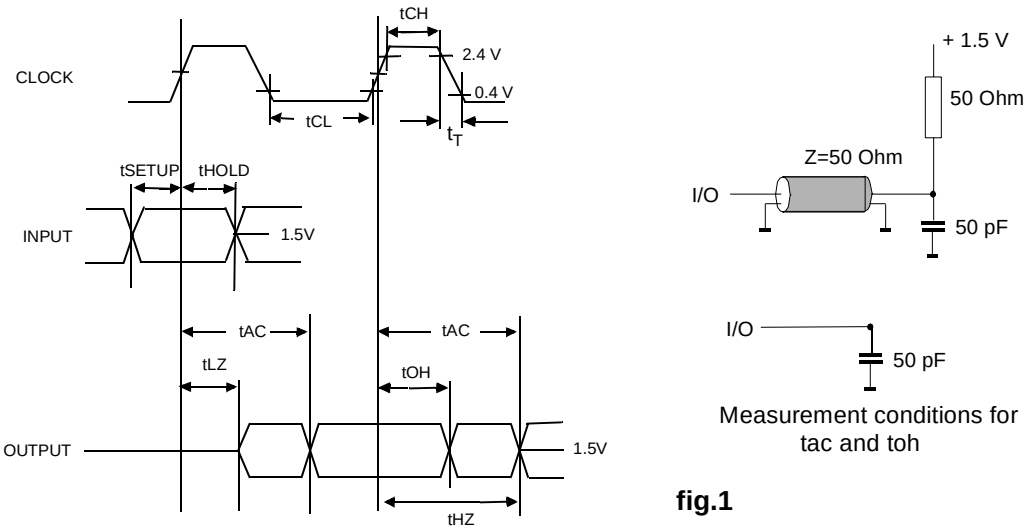


fig.1

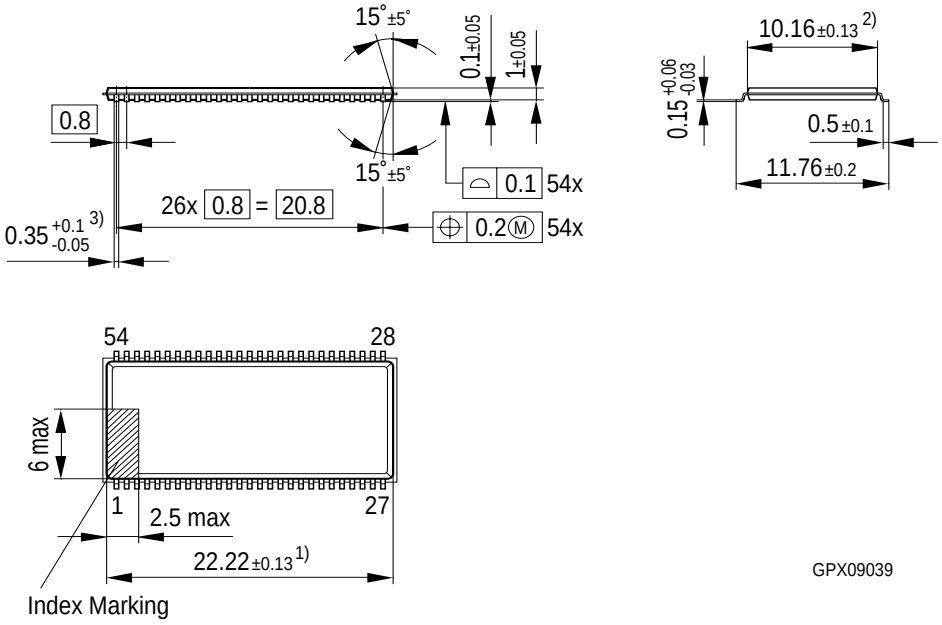
3. If clock rising time is longer than 1 ns, a time (t_T/2 - 0.5) ns has to be added to this parameter.
4. If tT is longer than 1 ns, a time (t_T -1) ns has to be added to this parameter.
5. These parameter account for the number of clock cycle and depend on the operating frequency of the clock, as follows:

   the number of clock cycle = specified value of timing period (counted in fractions as a whole number)

   Self Refresh Exit is a synchronous operation and begins on the 2nd positive clock edge after CKE returns high. Self Refresh Exit is not complete until a time period equal to tRC is satisfied once the Self Refresh Exit command is registered.

Package Outlines

Plastic Package P-TSOPII-54
(400 mil, 0.8 mm lead pitch)
Thin Small Outline Package, SMD

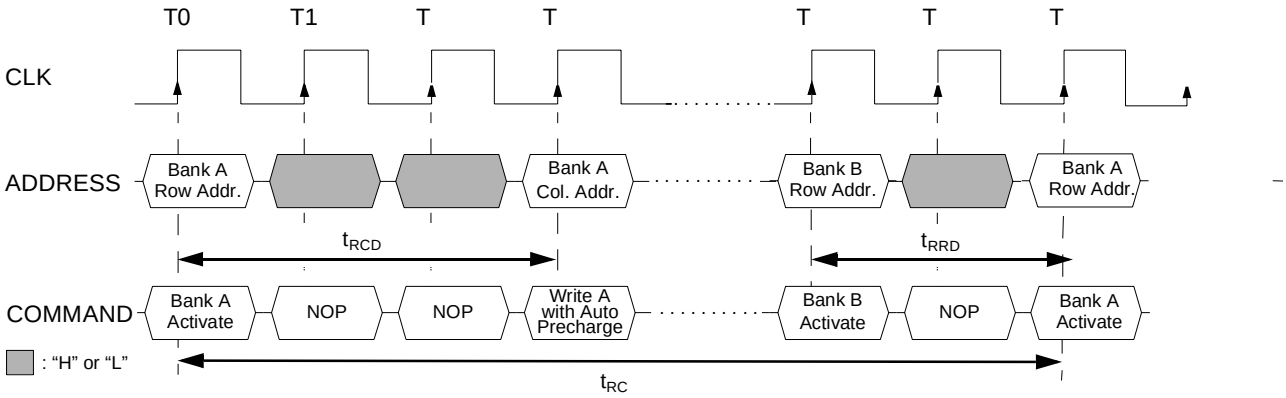


1) Does not include plastic or metal protrusion of 0.15 max per side
2) Does not include plastic protrusion of 0.25 max per side
3) Does not include dambar protrusion of 0.13 max per side

Timing Diagrams

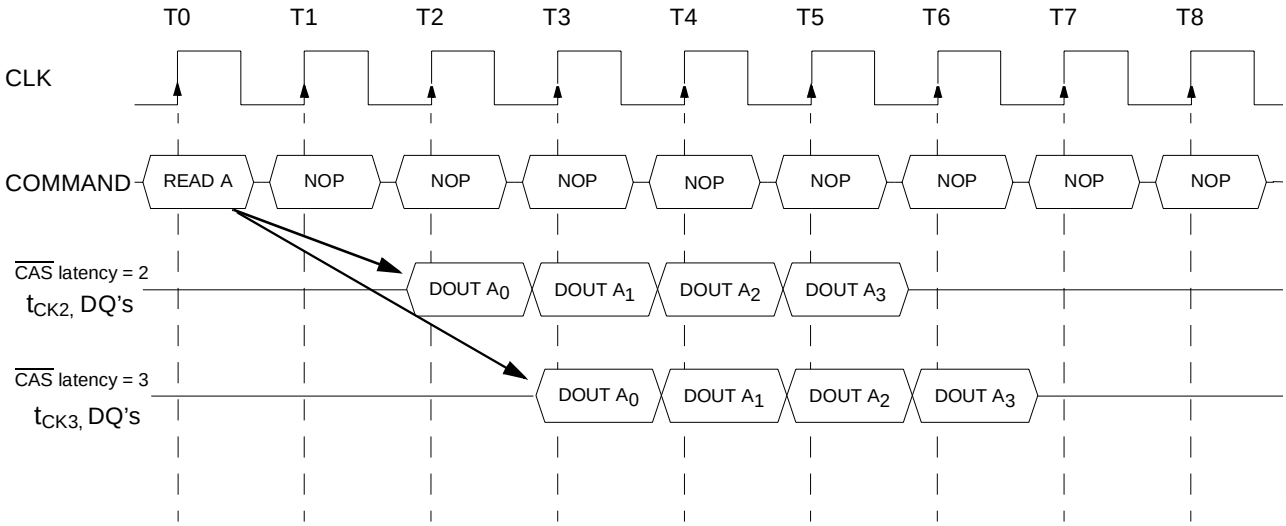
1. Bank Activate Command Cycle

($\overline{\text{CAS}}$ latency = 3)



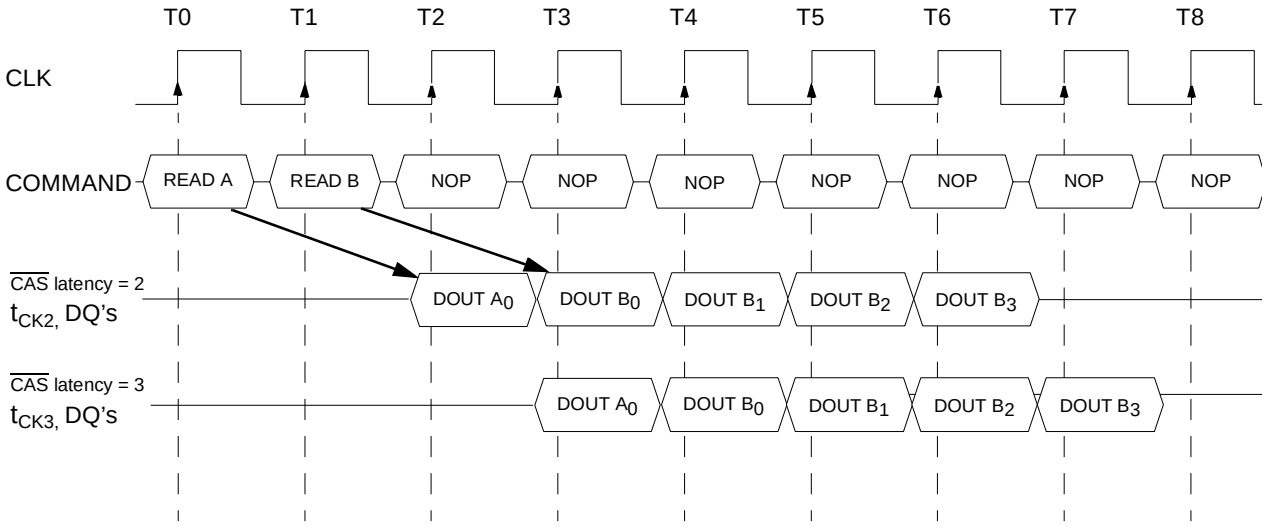
2. Burst Read Operation

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3)



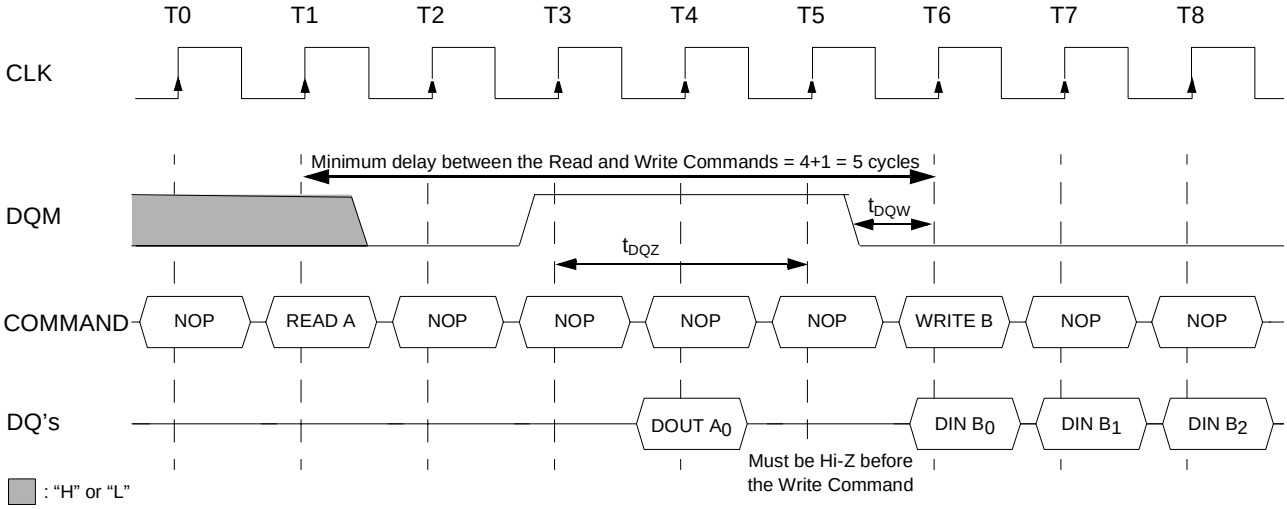
3. Read Interrupted by a Read

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3)



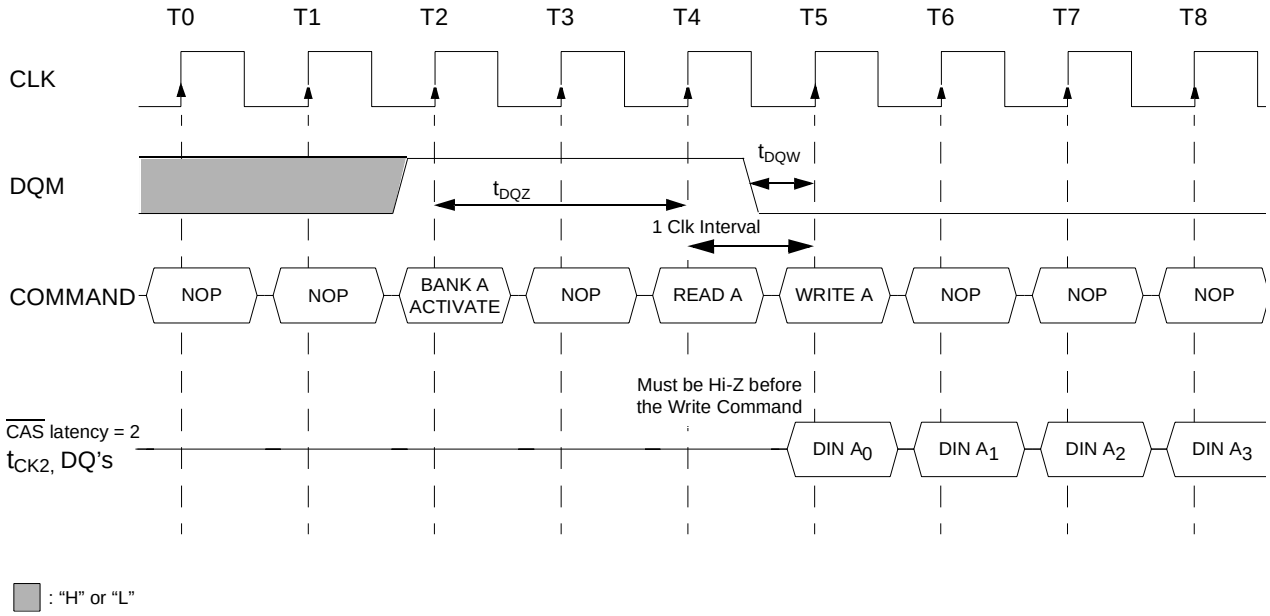
4.1 Read to Write Interval

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 3)



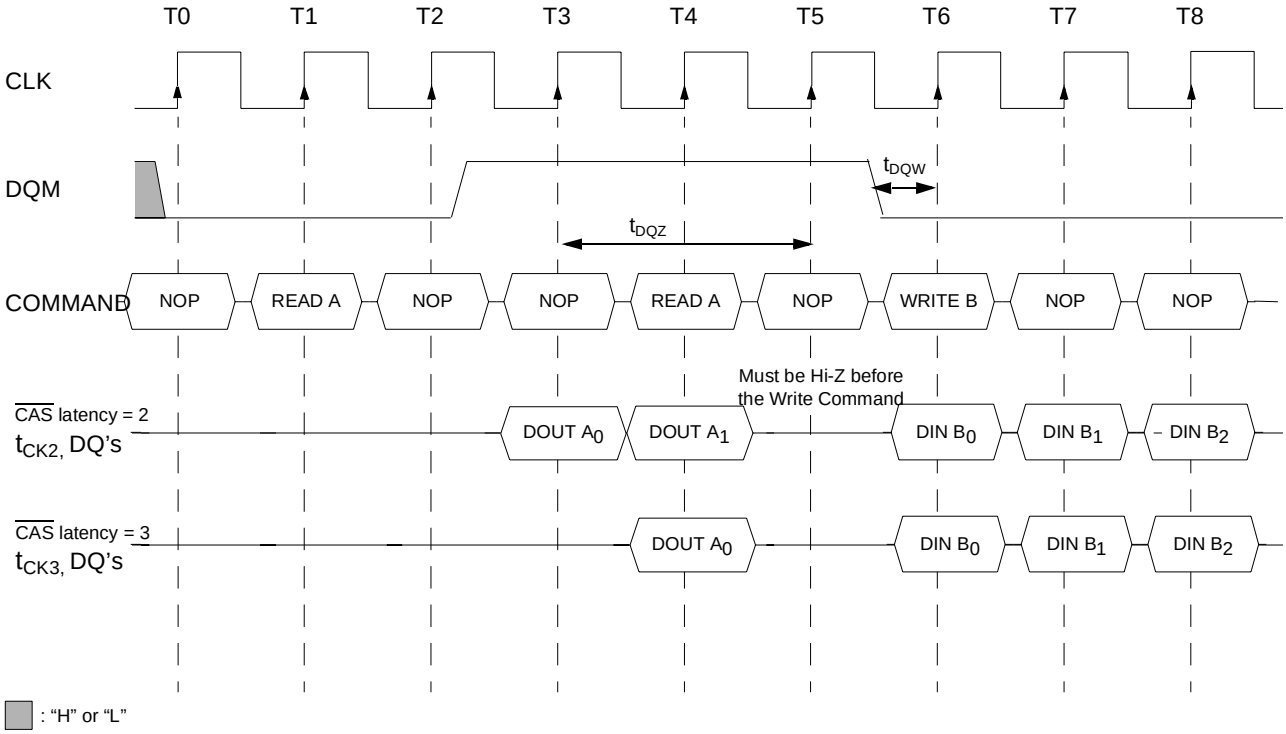
4 2. Minimum Read to Write Interval

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2)



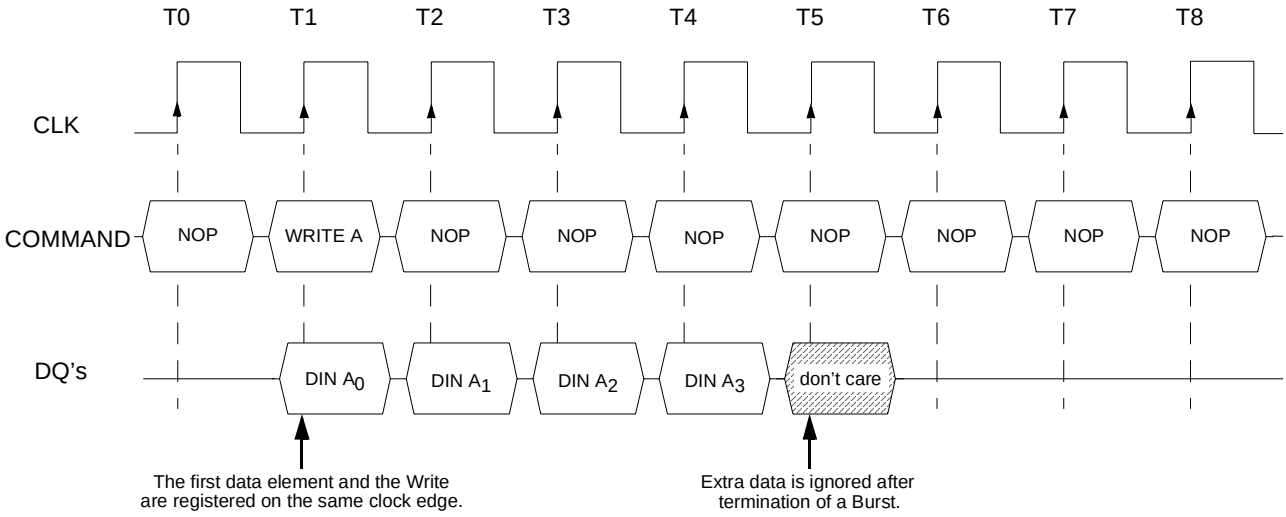
4. 3. Non-Minimum Read to Write Interval

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3



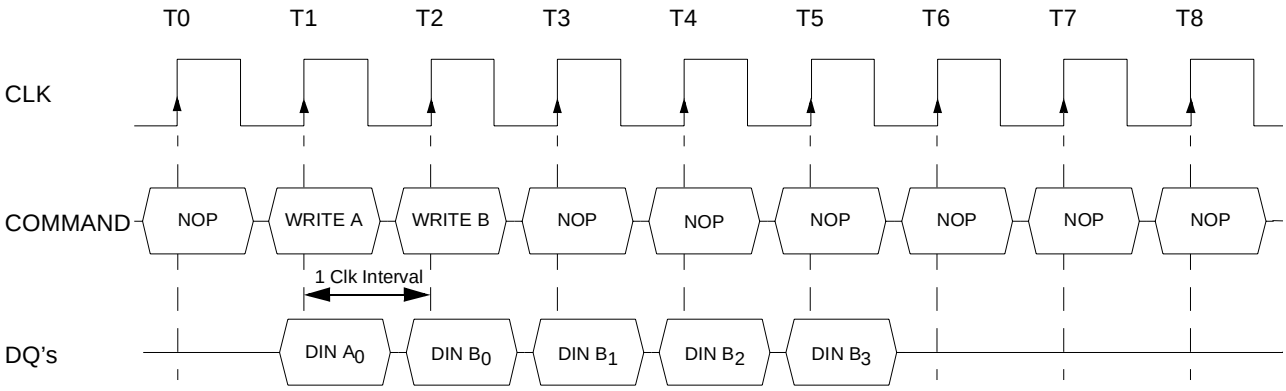
5. Burst Write Operation

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3)



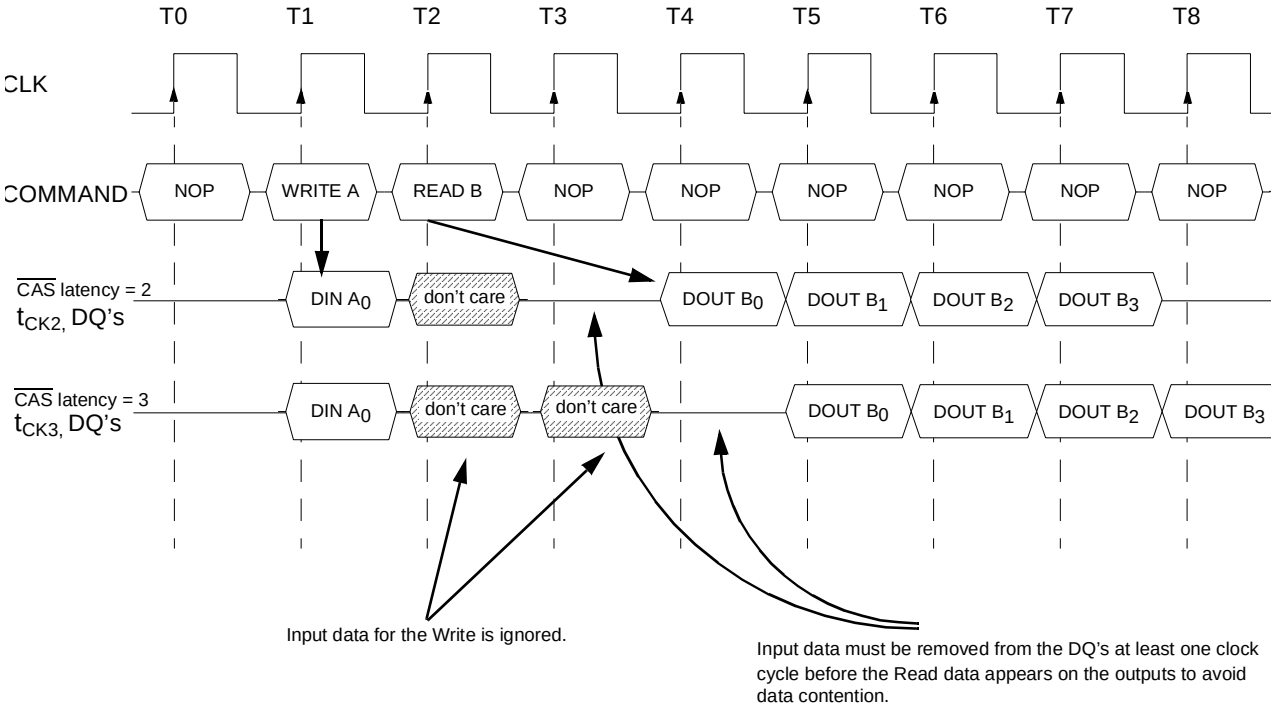
6.1 Write Interrupted by a Write

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3)



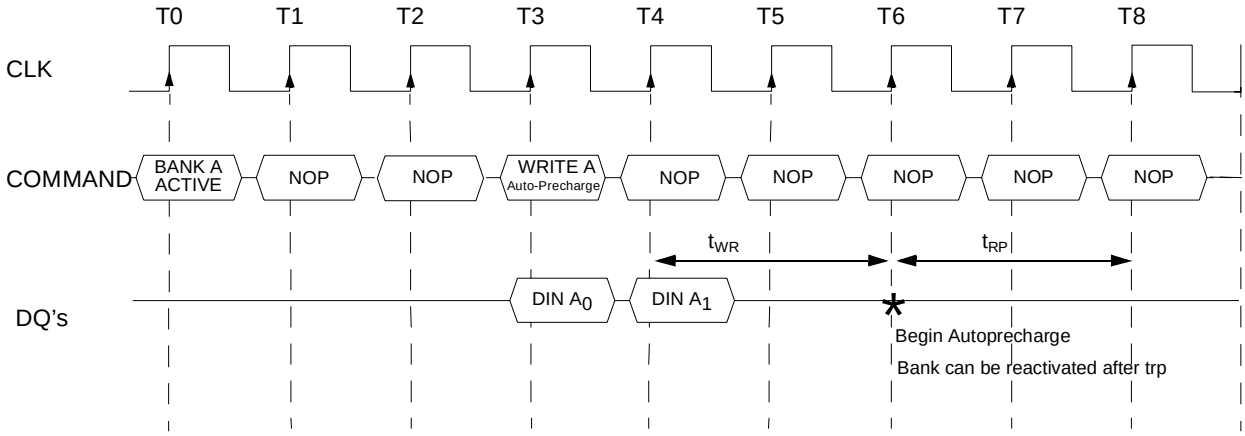
6.2 Write Interrupted by a Read

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3



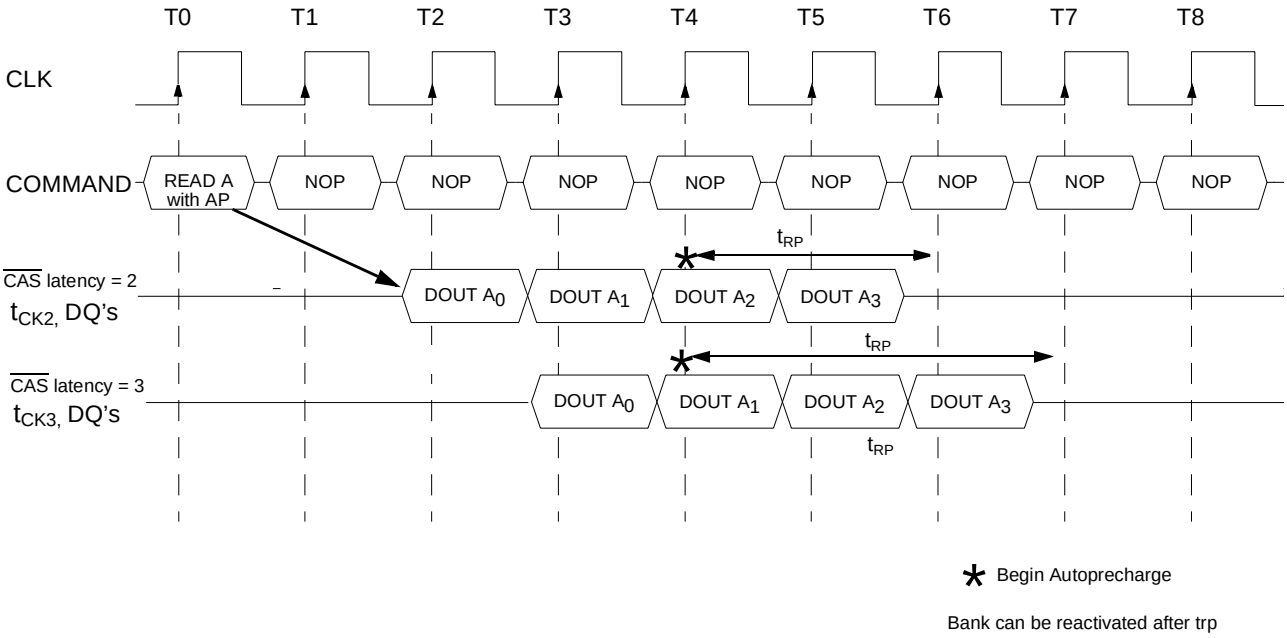
7.1 Burst Write with Auto-Precharge

Burst Length = 2, $\overline{\text{CAS}}$ latency = 2, 3)



7.2 Burst Read with Auto-Precharge

(Burst Length = 4, $\overline{\text{CAS}}$ latency = 2, 3)

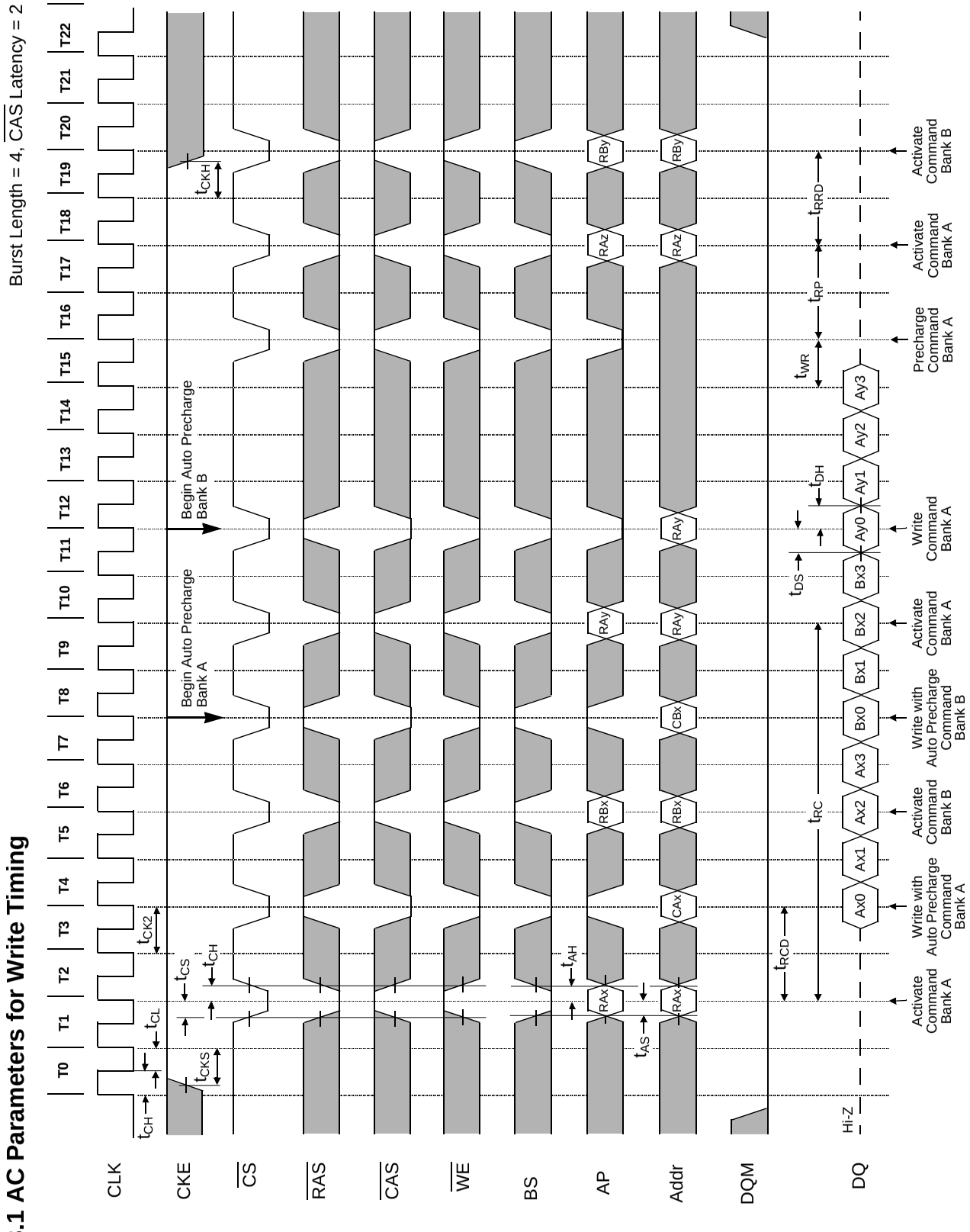


* Begin Autoprecharge

Bank can be reactivated after trp

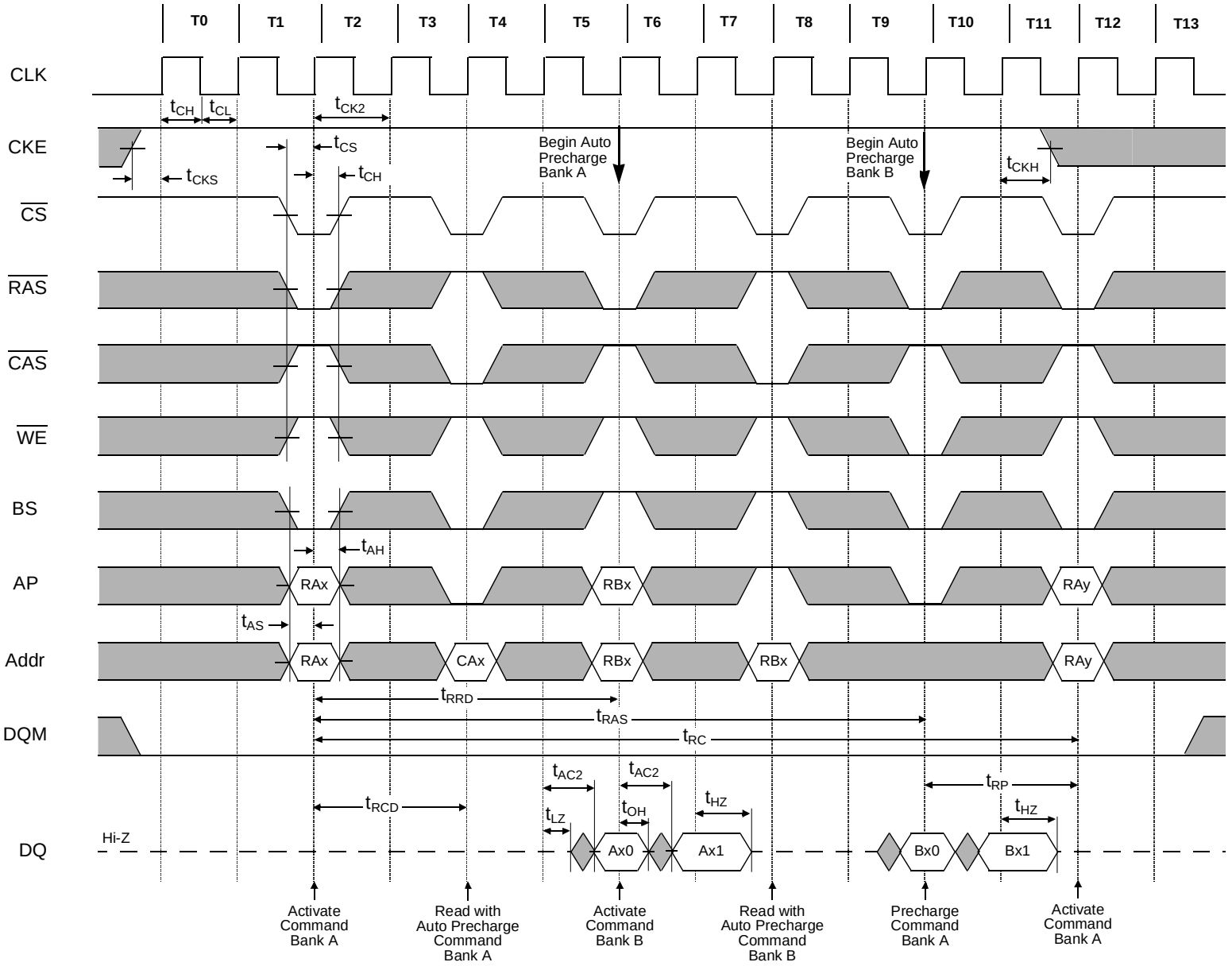
8.1 AC Parameters for Write Timing

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2

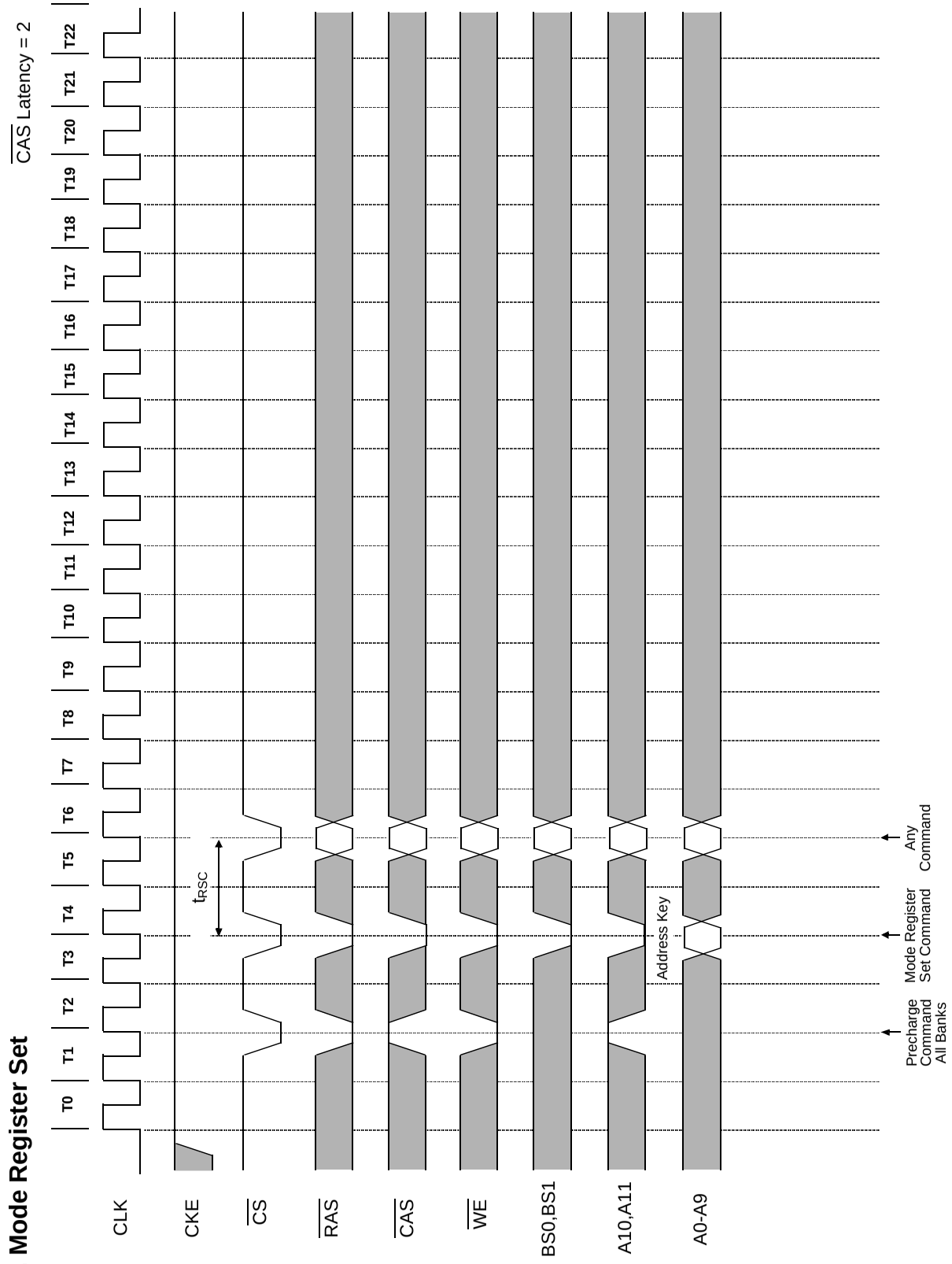


8.2 AC Parameters for Read Timing

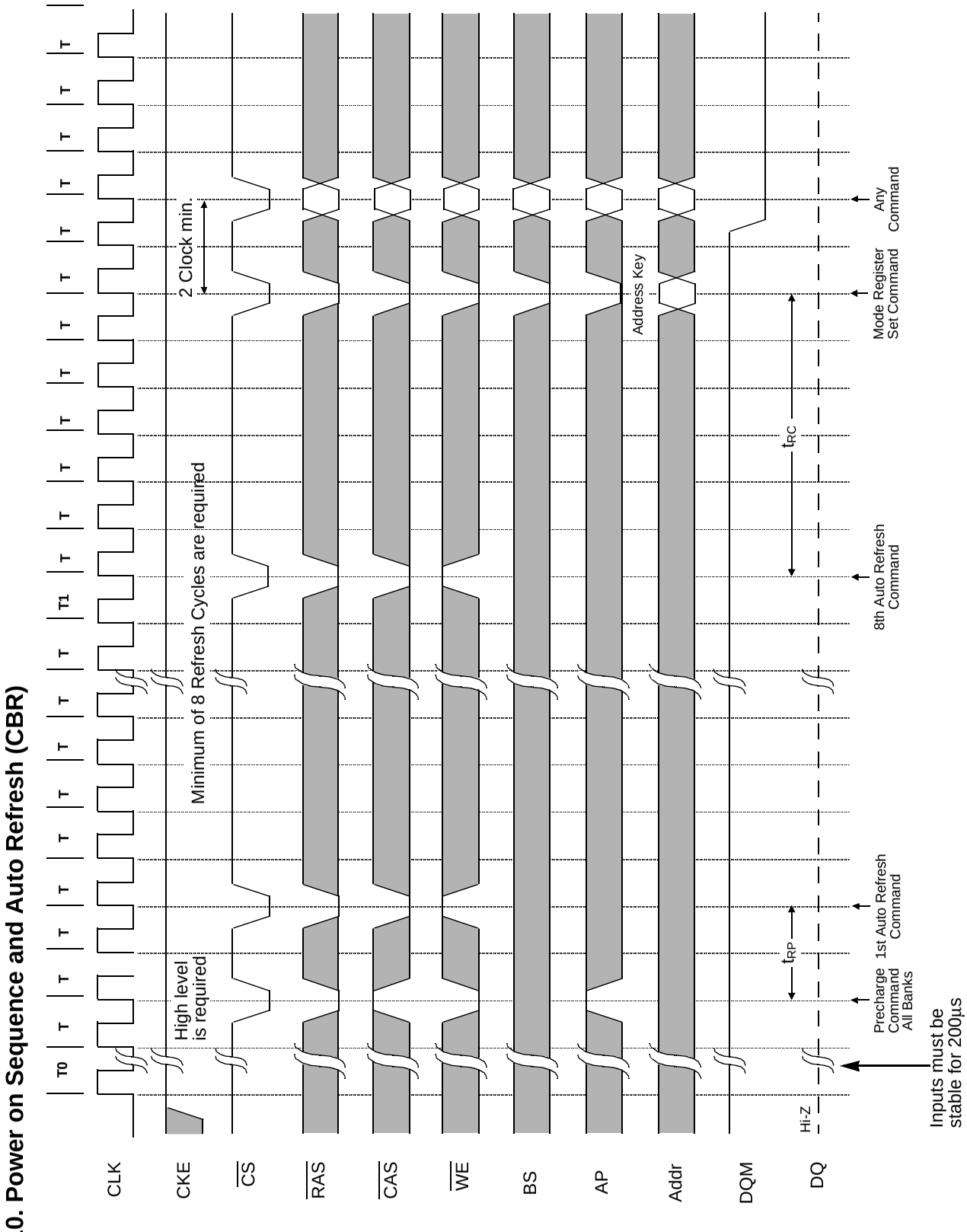
Burst Length = 2, $\overline{\text{CAS}}$ Latency = 2



9. Mode Register Set

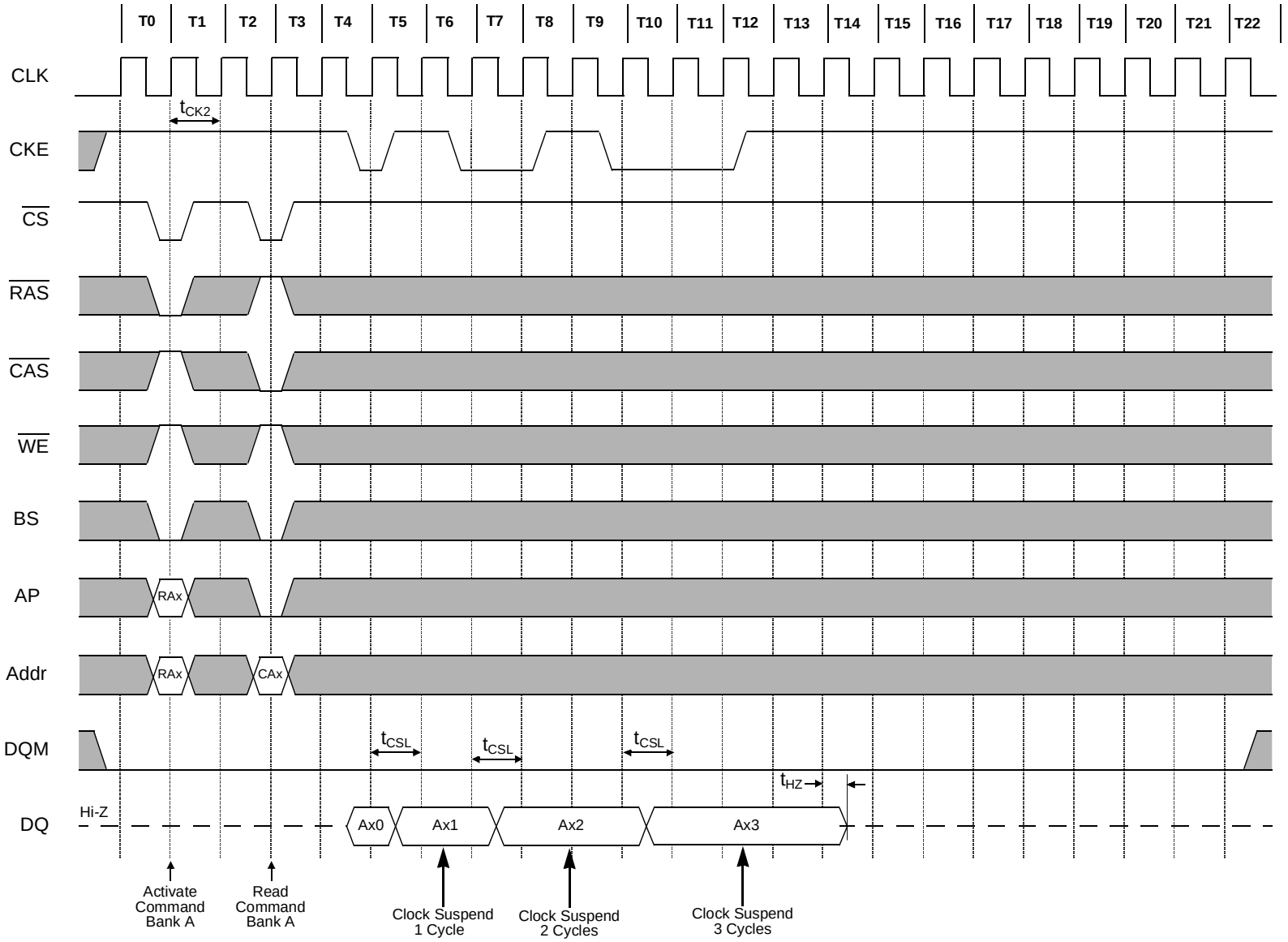


10. Power on Sequence and Auto Refresh (CBR)



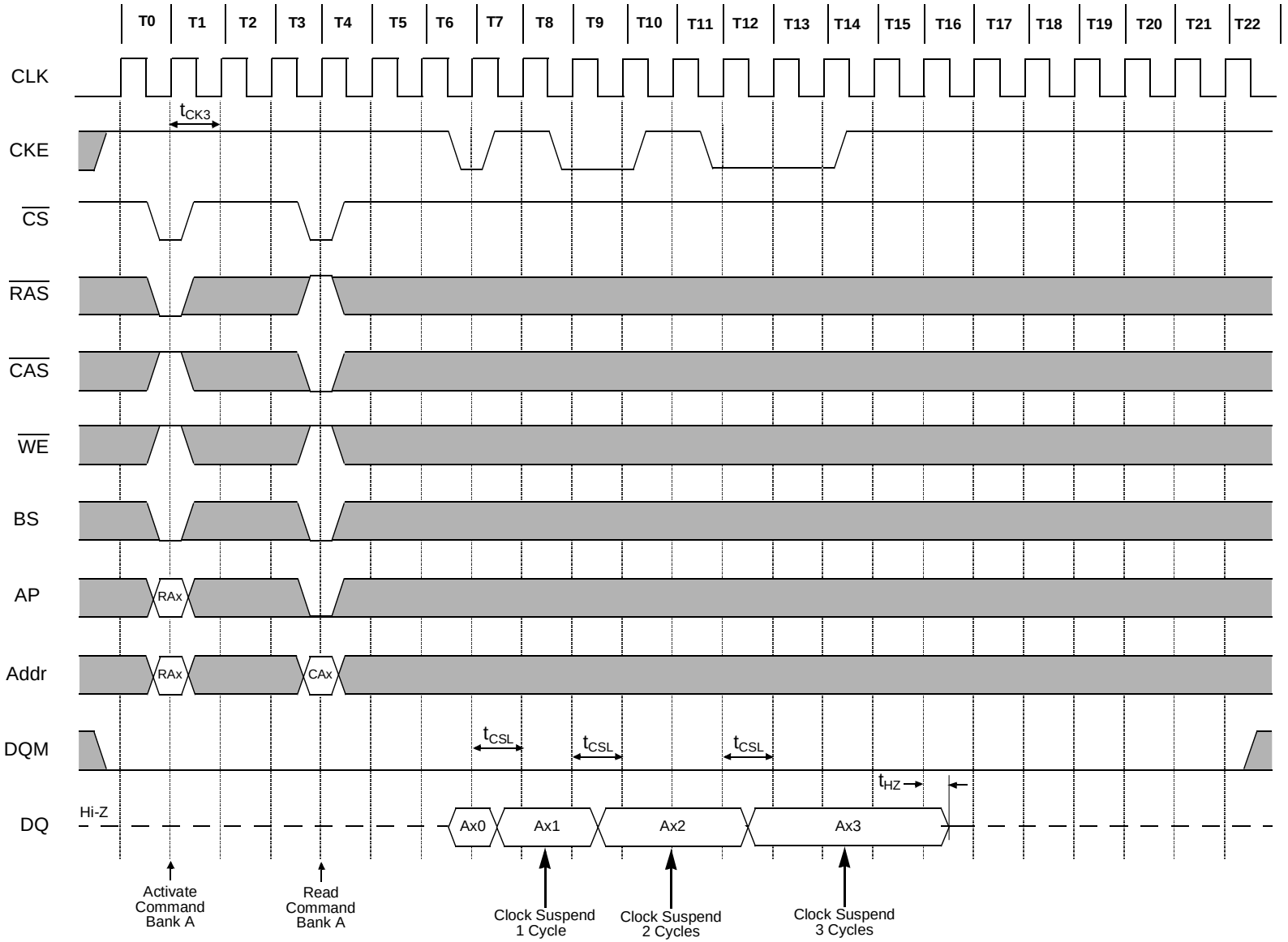
11.1 Clock Suspension During Burst Read (Using CKE)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2



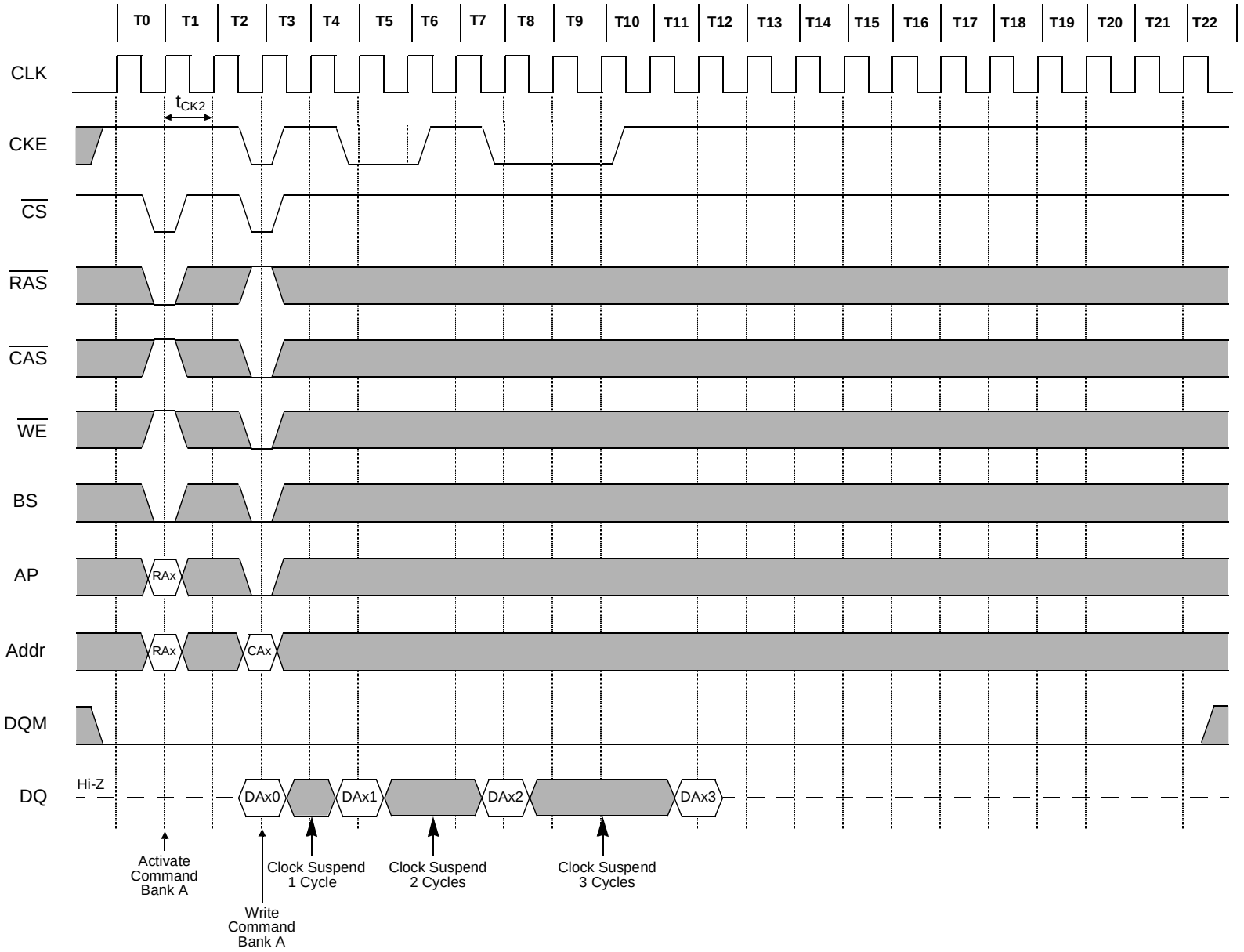
11.2 Clock Suspension During Burst Read (Using CKE)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 3



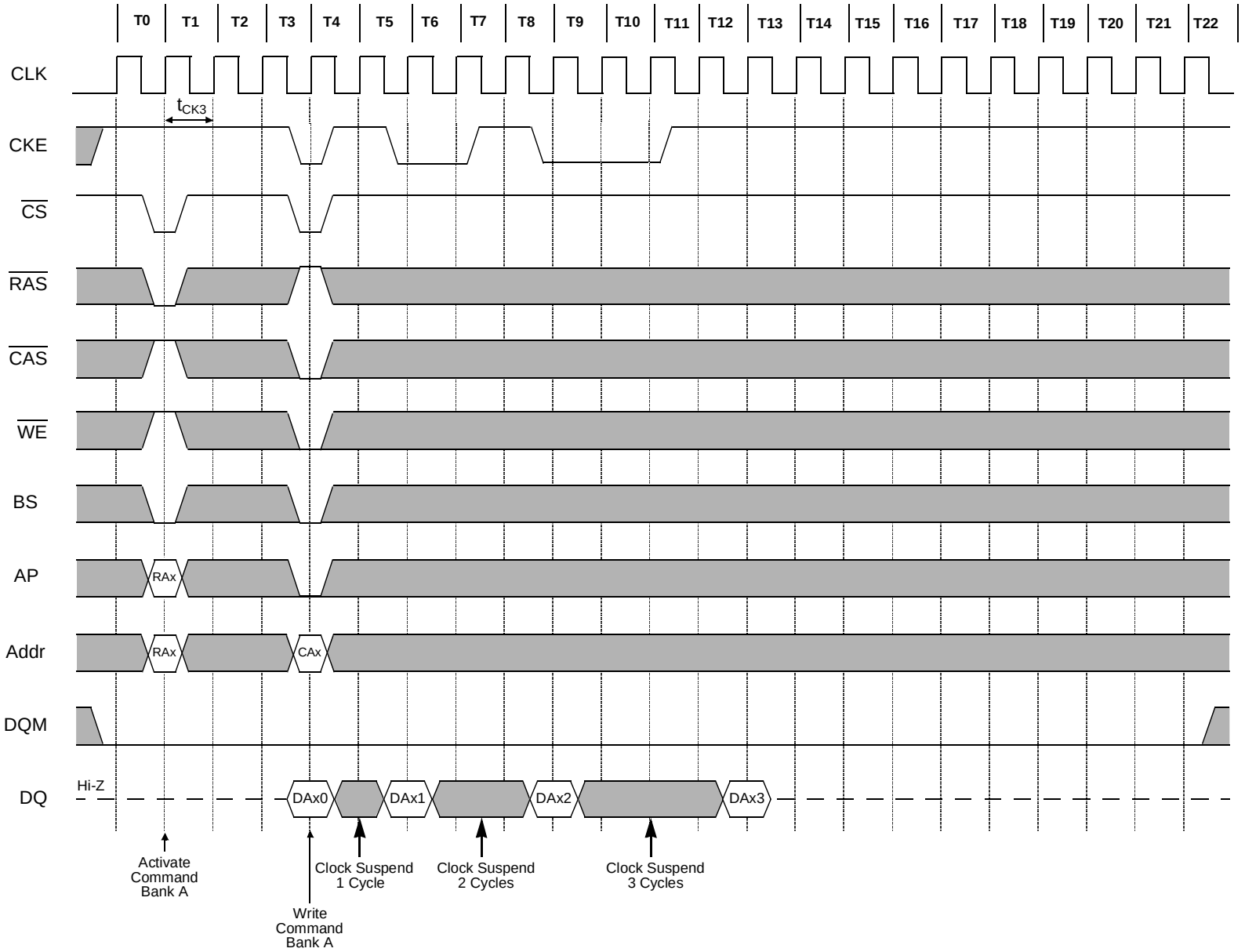
11.3 Clock Suspension During Burst Write (Using CKE)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2



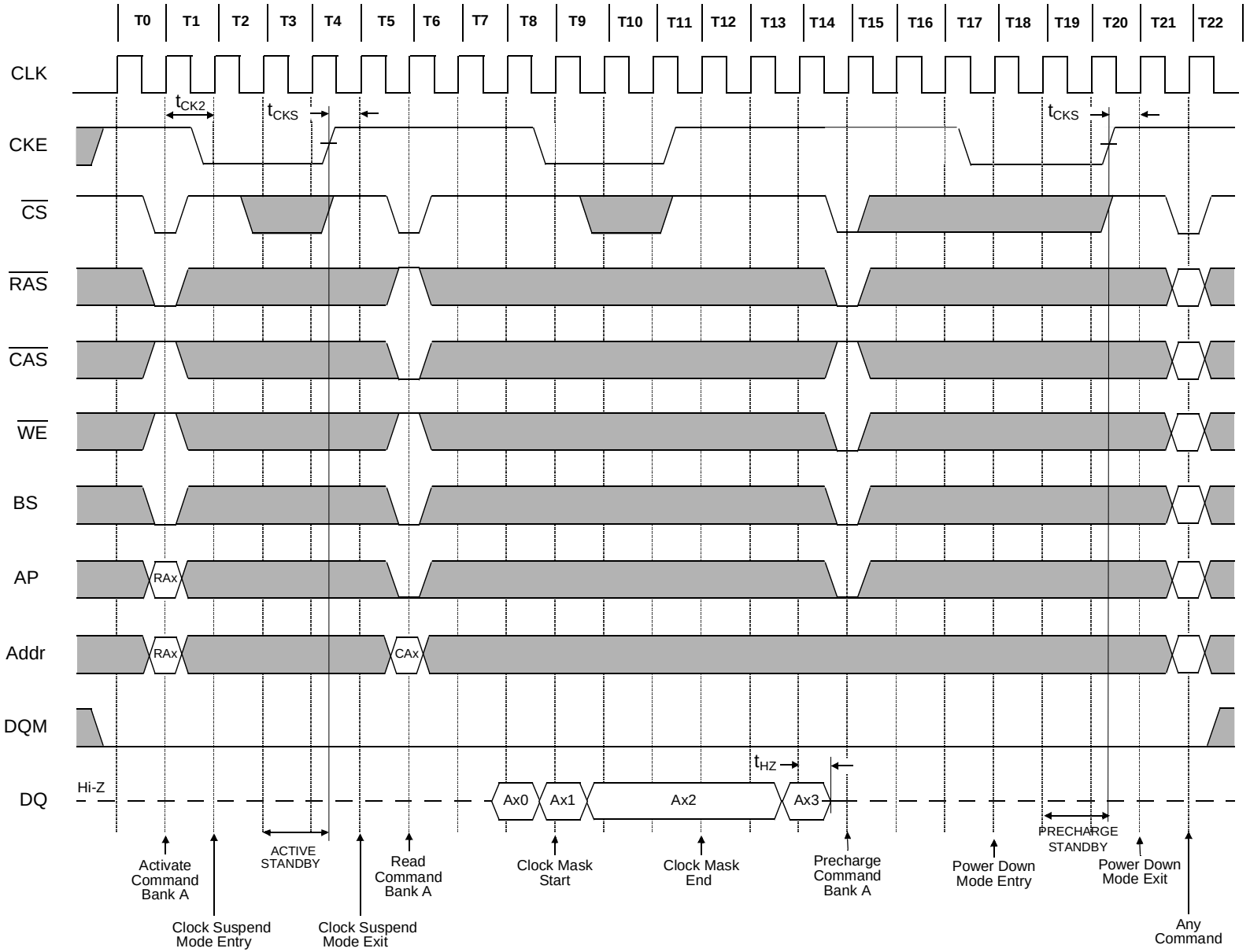
11.4 Clock Suspension During Burst Write (Using CKE)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 3

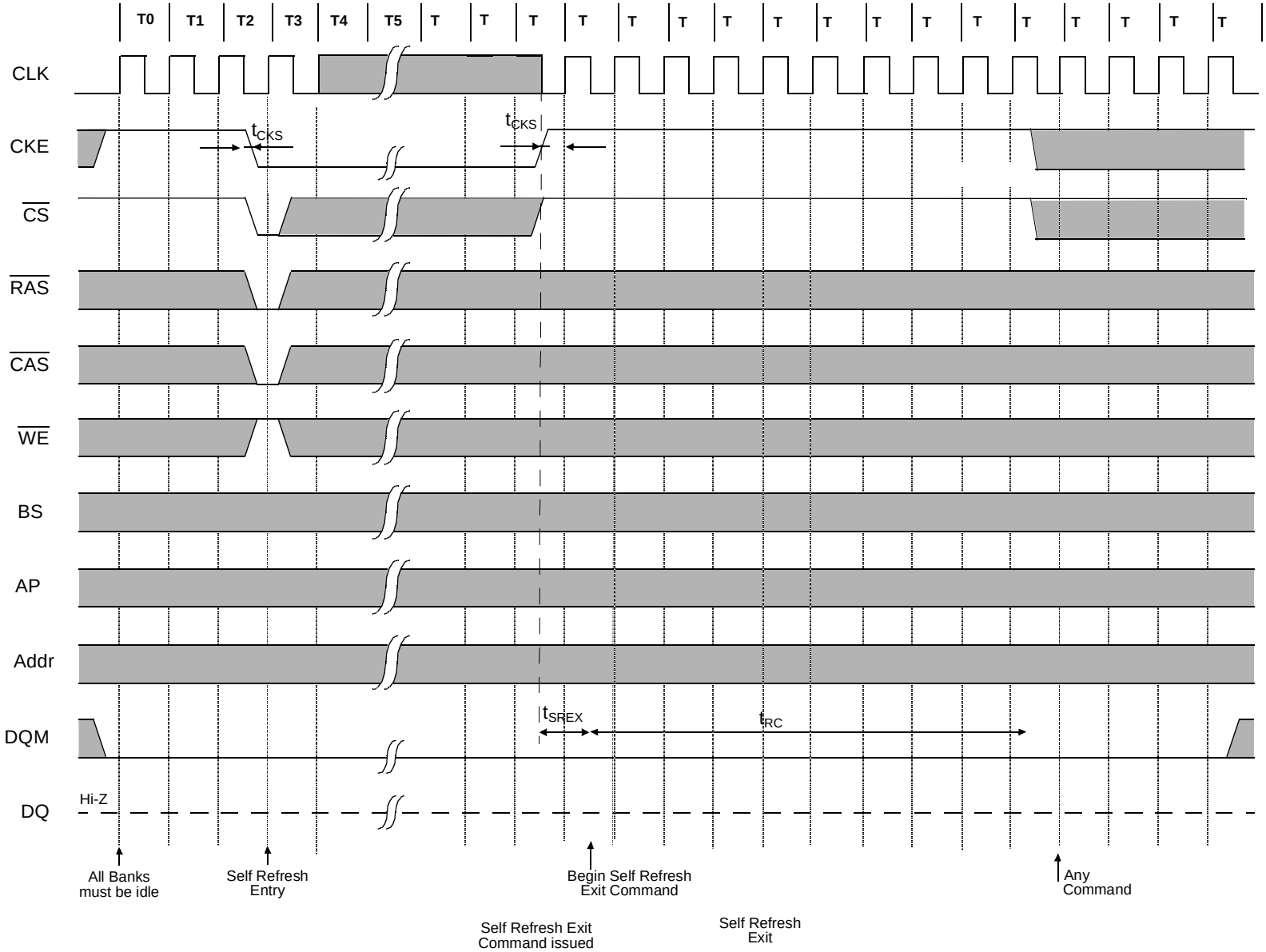


12. Power Down Mode and Clock Suspend

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2

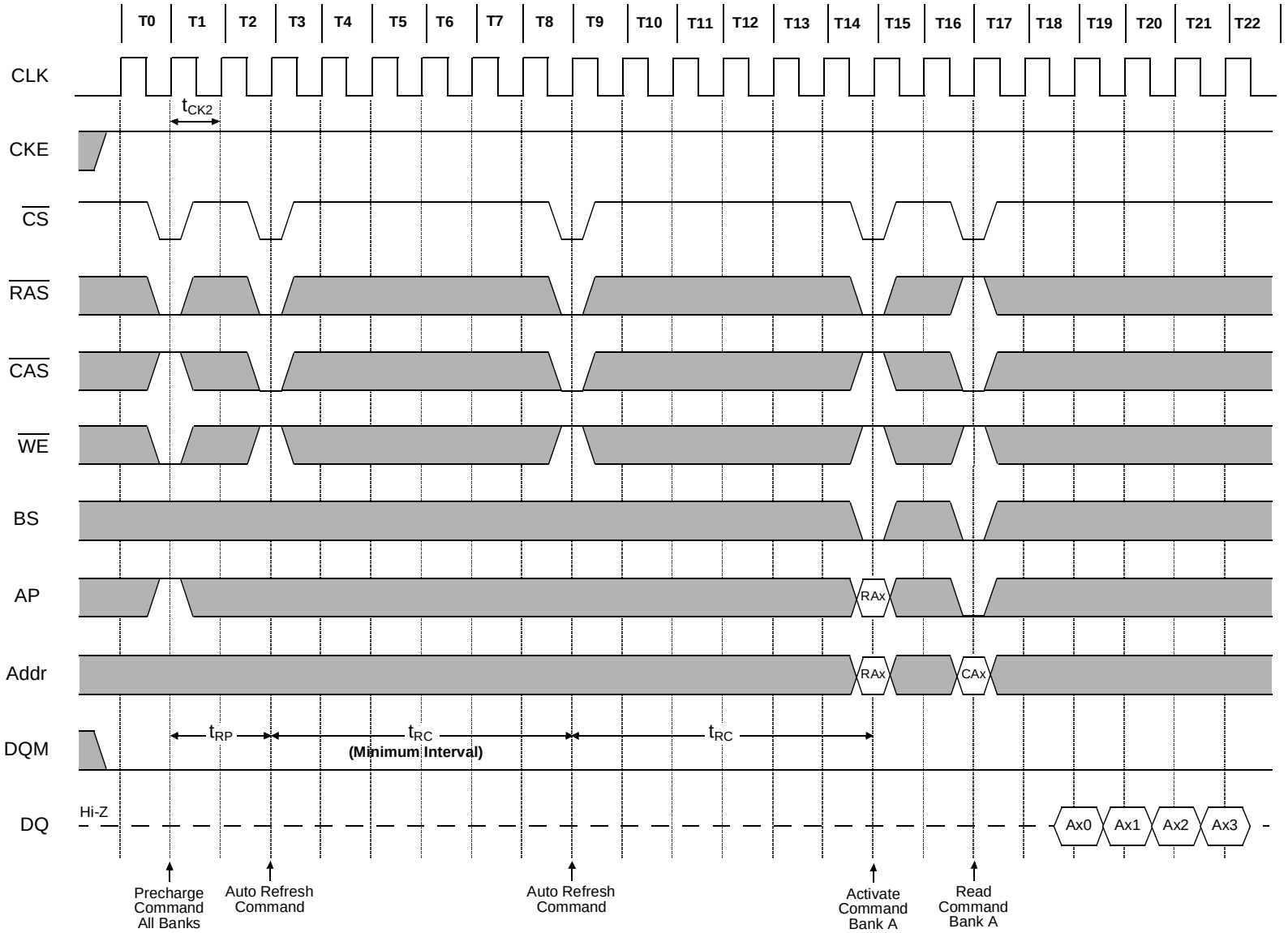


13. Self Refresh (Entry and Exit)



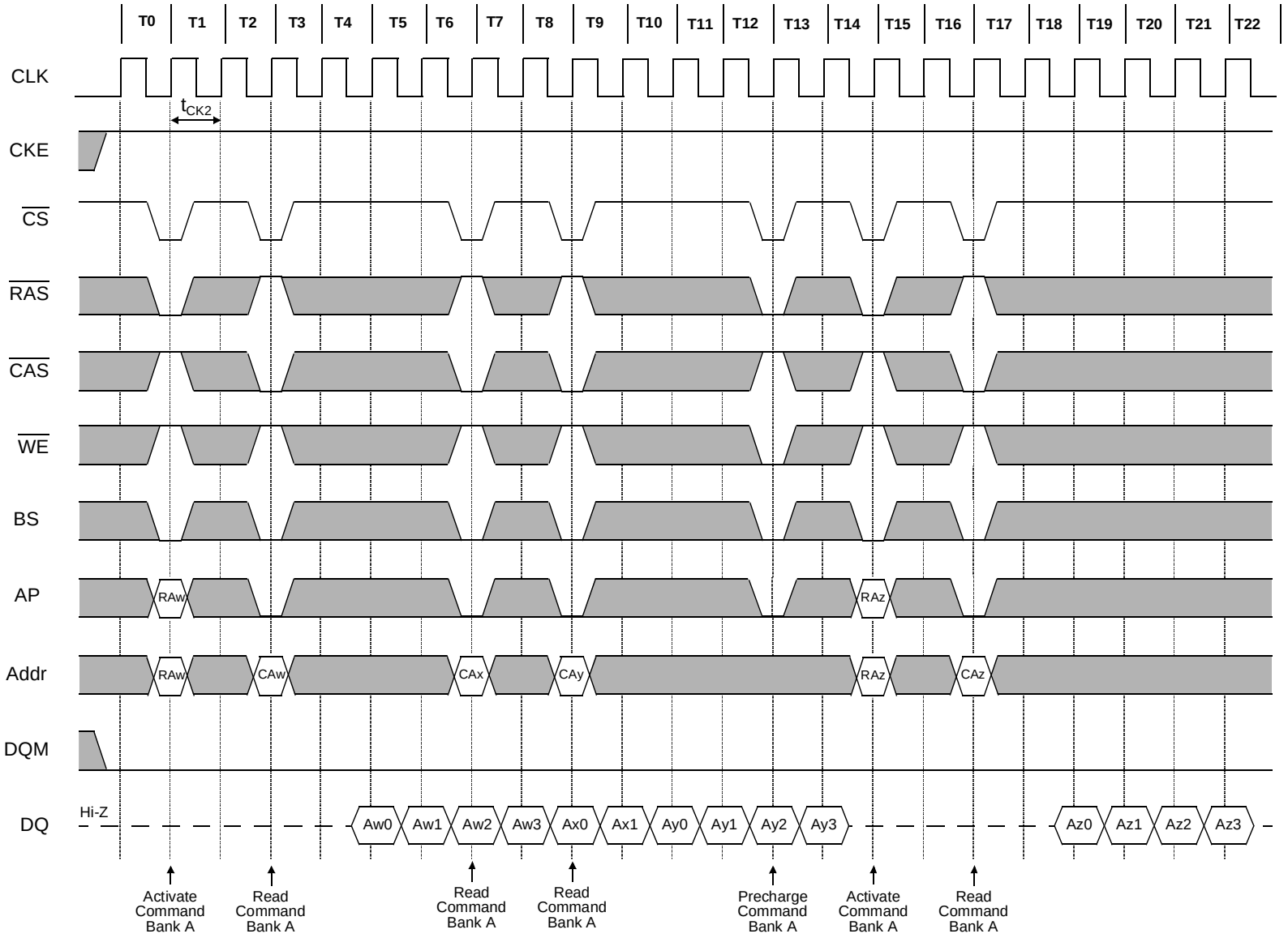
14. Auto Refresh (CBR)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2

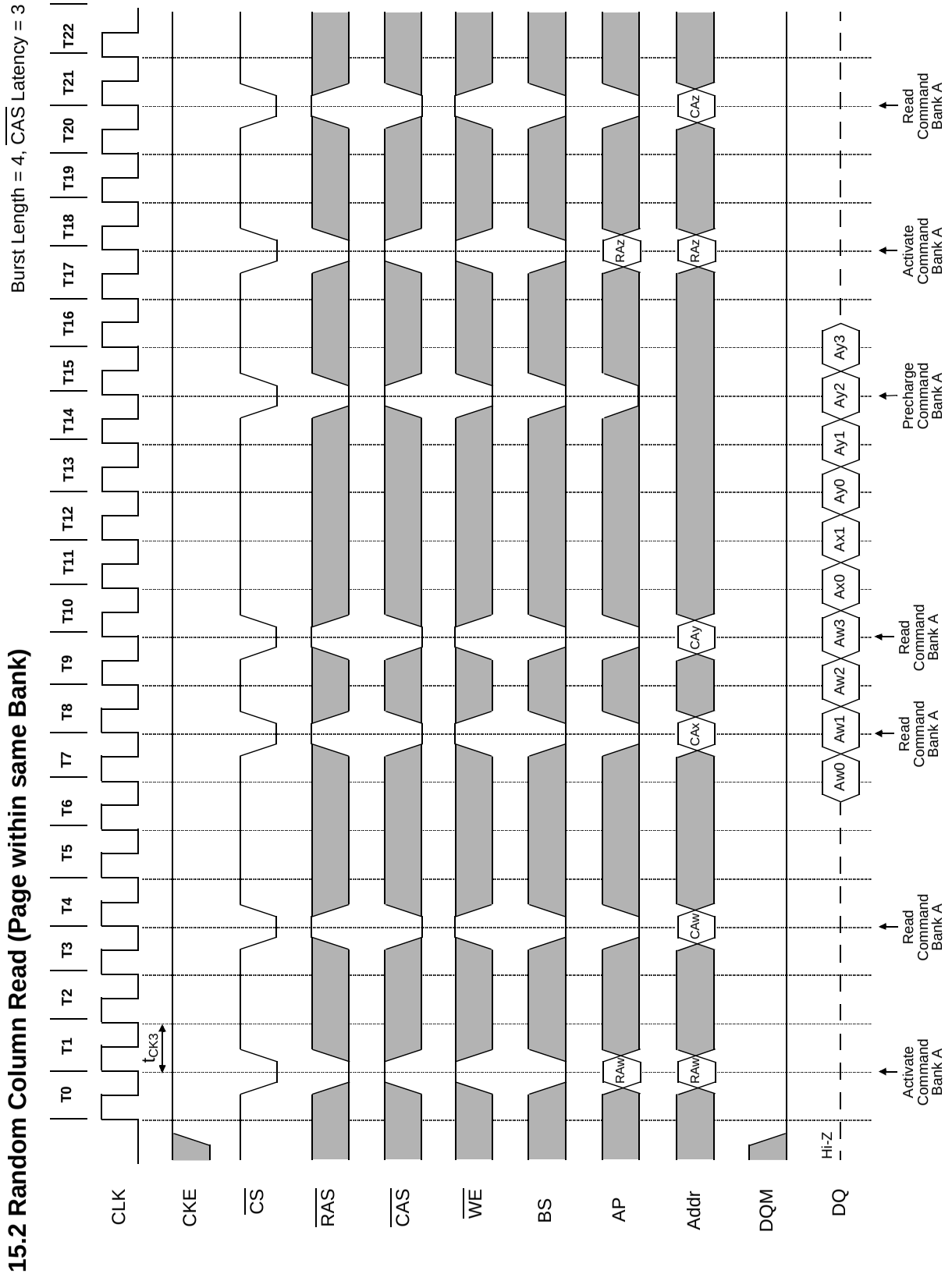


15.1 Random Column Read (Page within same Bank)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2

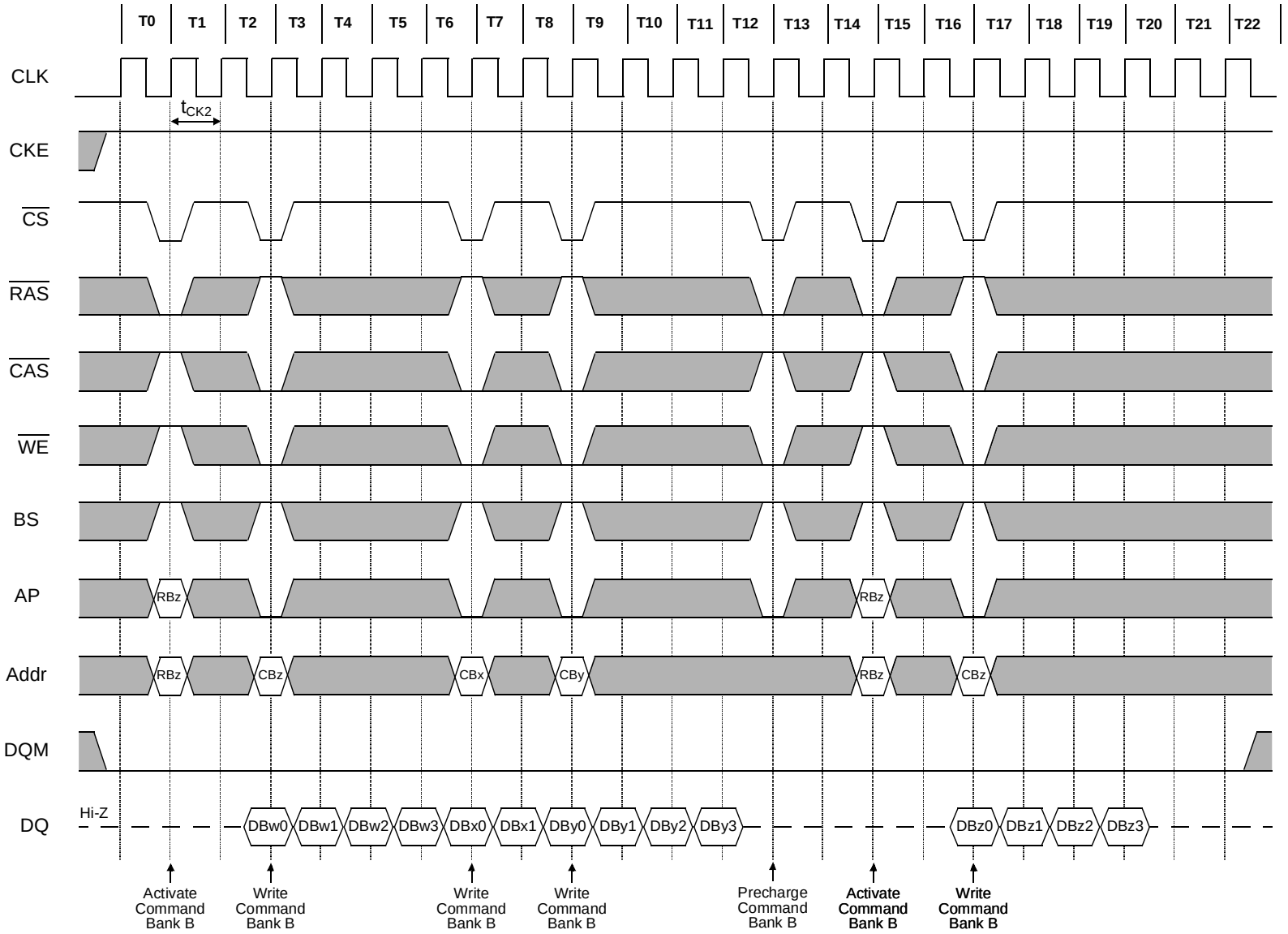


15.2 Random Column Read (Page within same Bank)



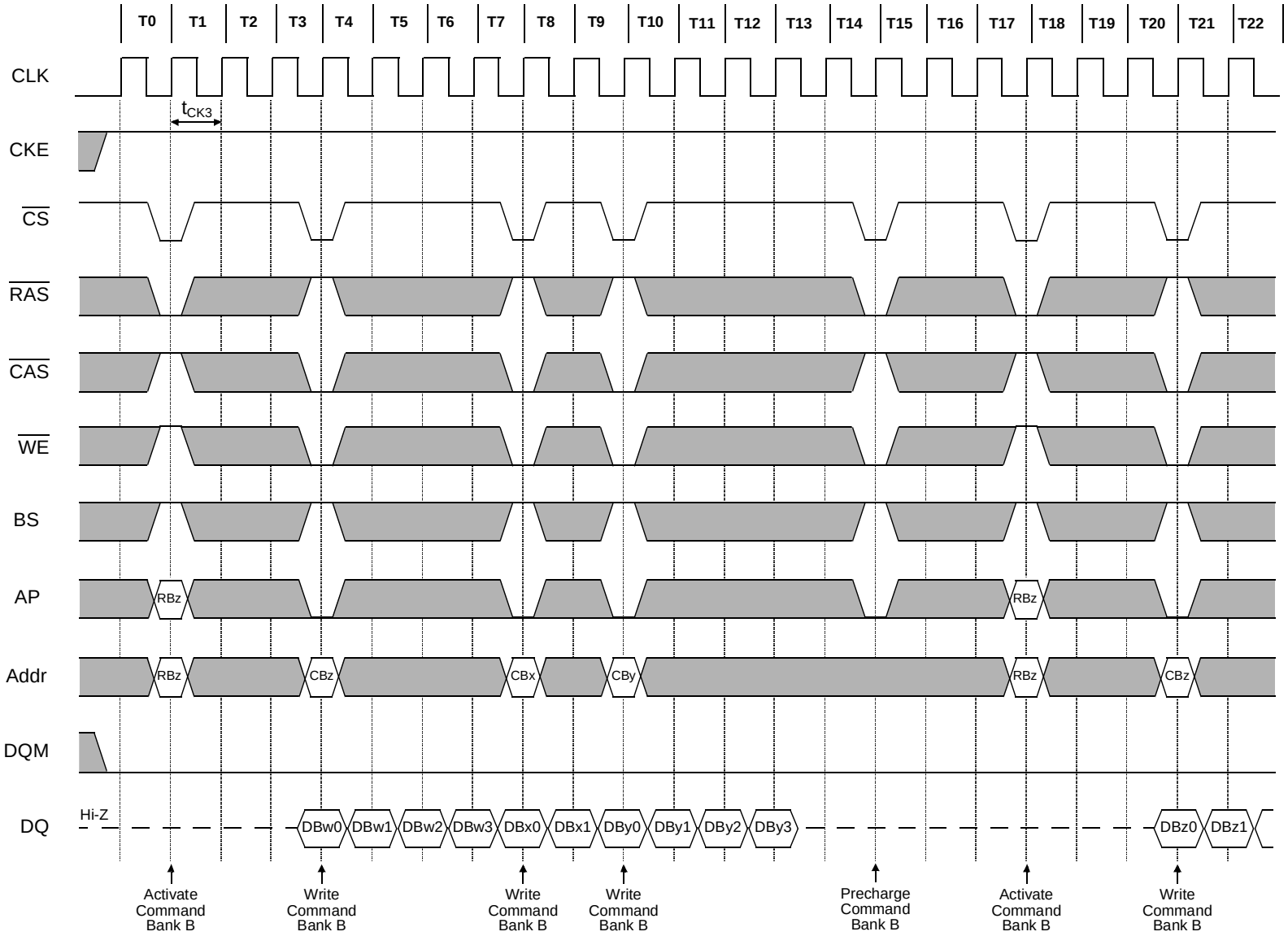
16.1 Random Column Write (Page within same Bank)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 2



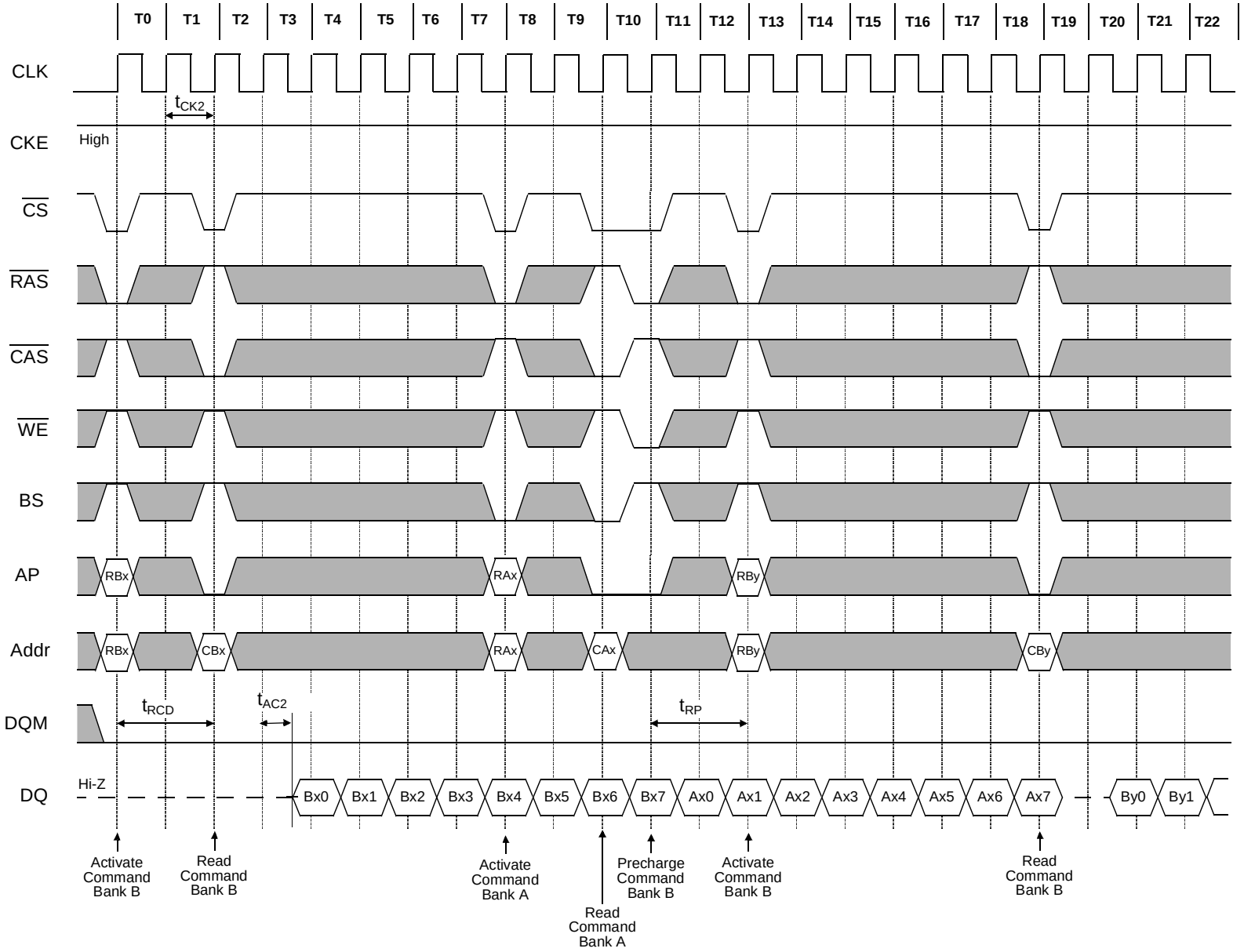
16.2 Random Column Write (Page within same Bank)

Burst Length = 4, $\overline{\text{CAS}}$ Latency = 3



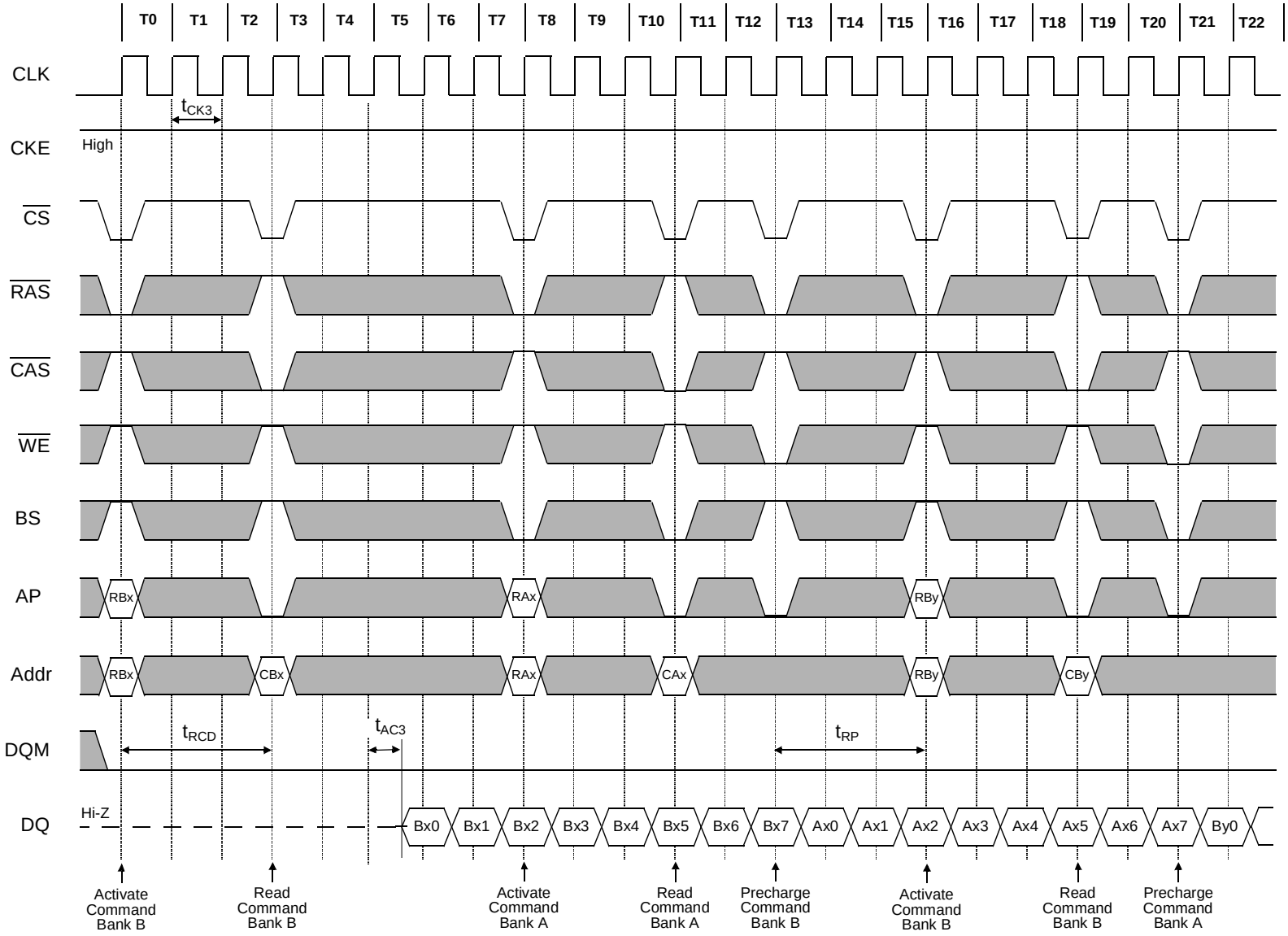
17.1 Random Row Read (Interleaving Banks) with Precharge

Burst Length = 8, $\overline{\text{CAS}}$ Latency = 2



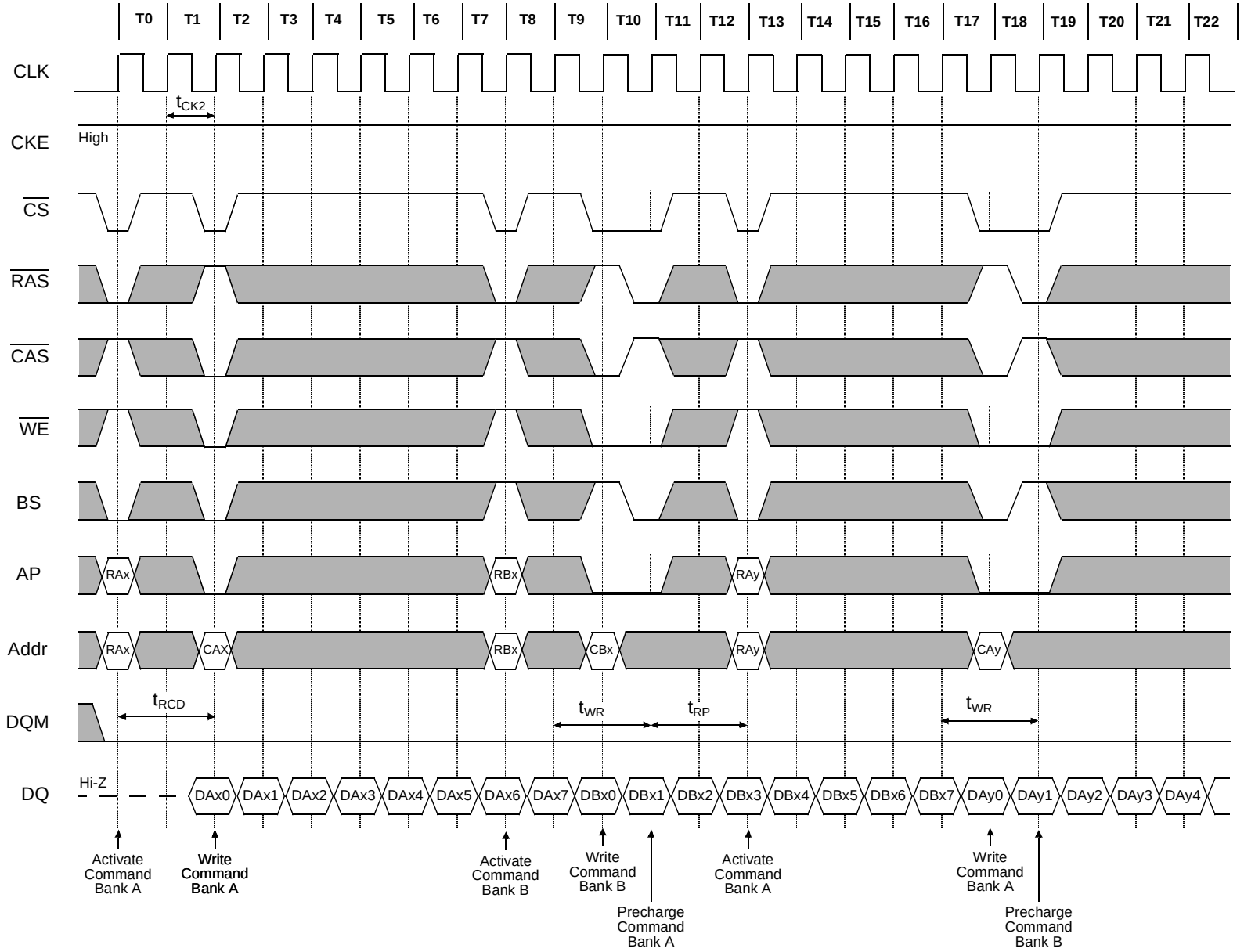
17.2 Random Row Read (Interleaving Banks) with Precharge

Burst Length = 8, $\overline{\text{CAS}}$ Latency = 3



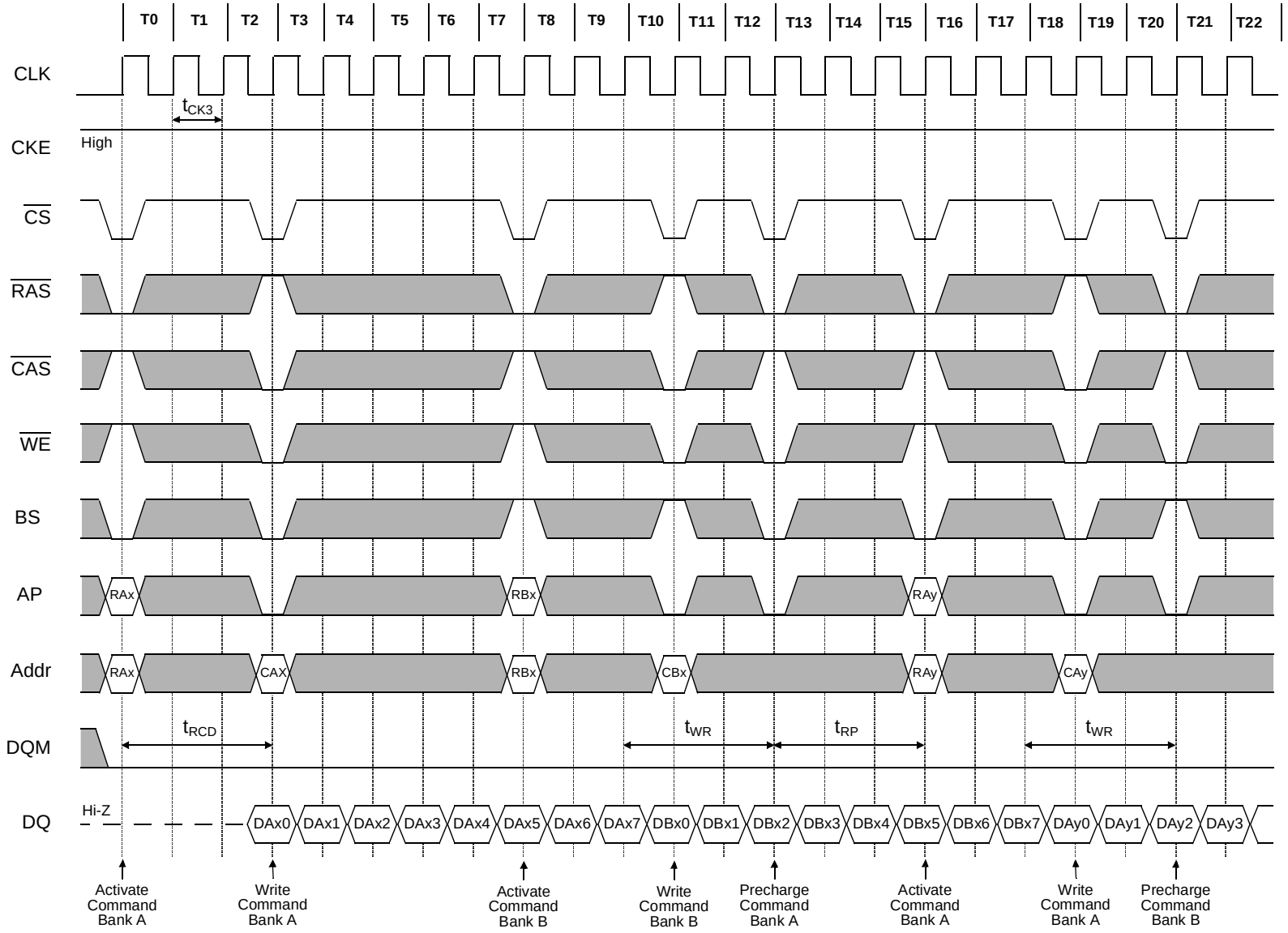
18.1 Random Row Write (Interleaving Banks) with Precharge

Burst Length = 8, $\overline{\text{CAS}}$ Latency = 2



18.2 Random Row Write (Interleaving Banks) with Precharge

Burst Length = 8, $\overline{\text{CAS}}$ Latency = 3



19. Precharge Termination of a Burst

Burst Length = 8 , $\overline{\text{CAS}}$ Latency = 2